

Optoelectronică, structuri și tehnologii

Curs 9

2016/2017

Disciplina 2016/2017

- ▶ 2C/1L Optoelectrică, structuri, tehnologii, circuite,
OSTC
- ▶ **Minim 7 prezente curs + laborator**
- ▶ Curs – **sl. Radu Damian**
 - Joi 15–18, P5
 - E – 70% din nota
 - **20% test la curs**, saptamana 4–5?
 - probleme + (**?1** subiect teorie) + (2p prez. Curs)
 - **2prez=0.5p**
 - **toate materialele permise**
- ▶ Laborator – **sl. Daniel Matasaru**
 - Joi 8-14 par
 - L – 15% din nota
 - C – 15% din nota

Recapitulare

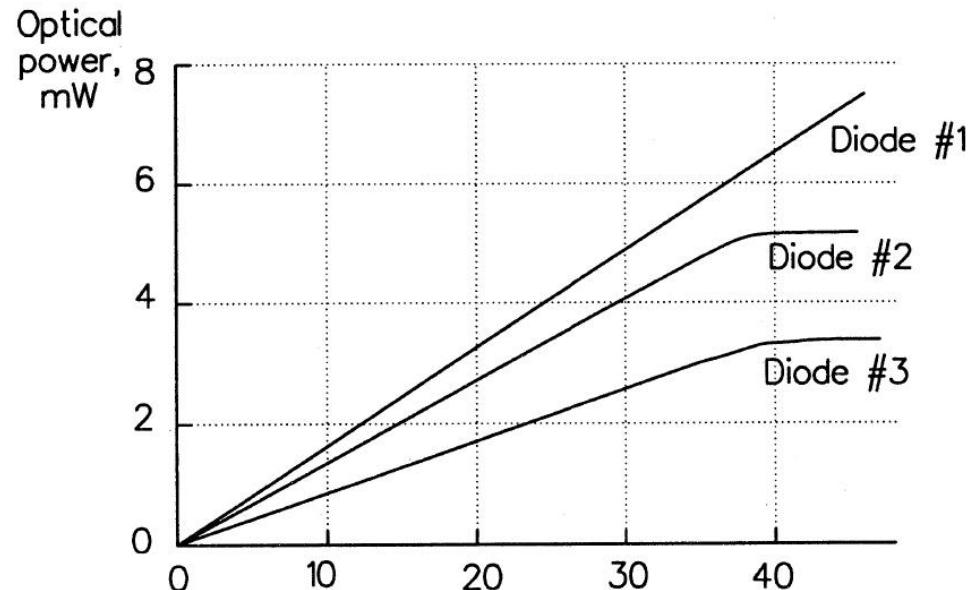
Curs 8

Caracteristica de raspuns a LED-urilor

- ▶ Caracteristica putere optica emisa functie de curentul direct prin LED este liniara la nivele mici ale curentului.
- ▶ Nu exista curent de prag
- ▶ La nivele foarte mari puterea optica se satureaza
- ▶ Rezonabilitatea

$$r = \frac{P_o}{I} \quad \left[\frac{W}{A} \right]$$

- ▶ Tipic $r=50\mu W/mA$



Caracteristica de raspuns a DL

- ▶ Amorsarea emisiei stimulate necesita pomparea unei anumite cantitati de energie – curent de prag

$I < I_{th}$ regim LED

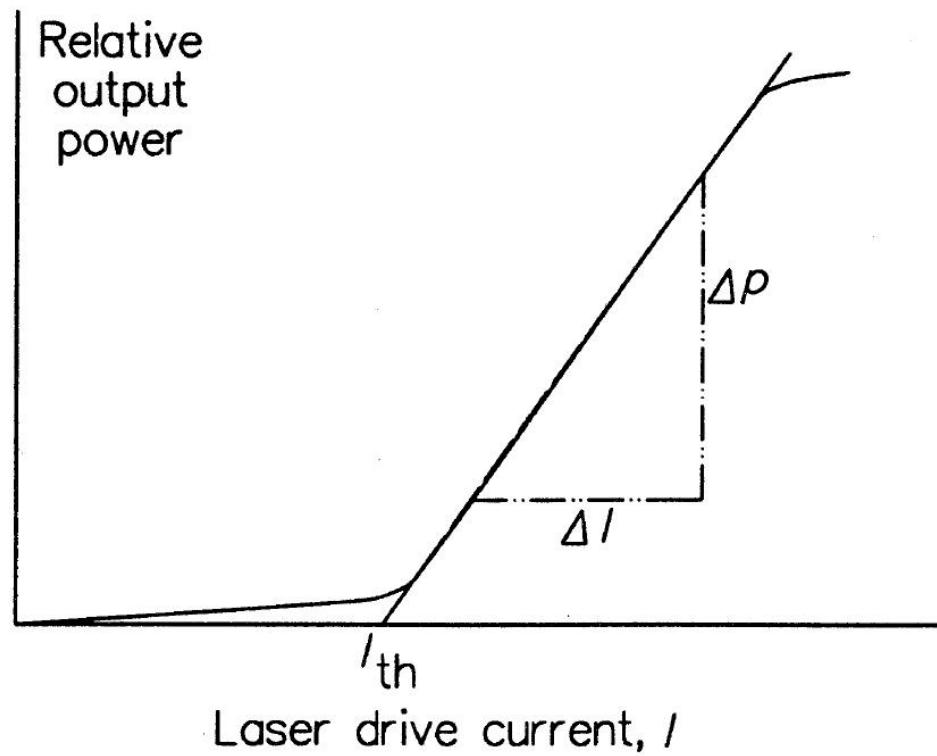
ineficient!, $P_o \approx 0$

$I > I_{th}$ regim LASER

$$r = \frac{\Delta P_o}{\Delta I} \left[\frac{W}{A} \right]$$

$$P_o = r \cdot (I - I_{th})$$

Apare saturare la nivele mari de curent



Fotodioda

Capitolul 9

Detectori optici

► Cerinte

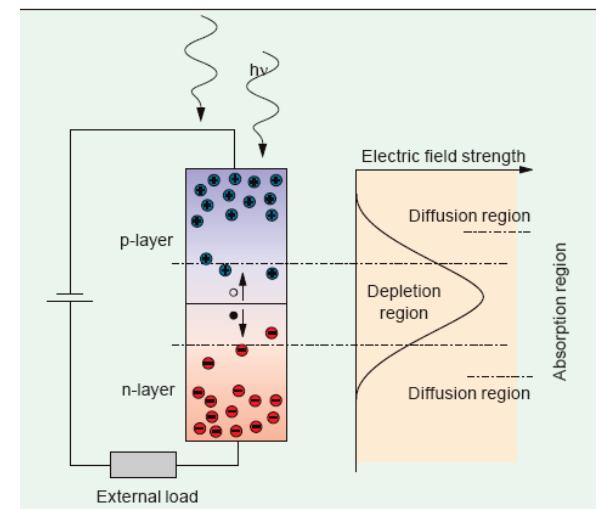
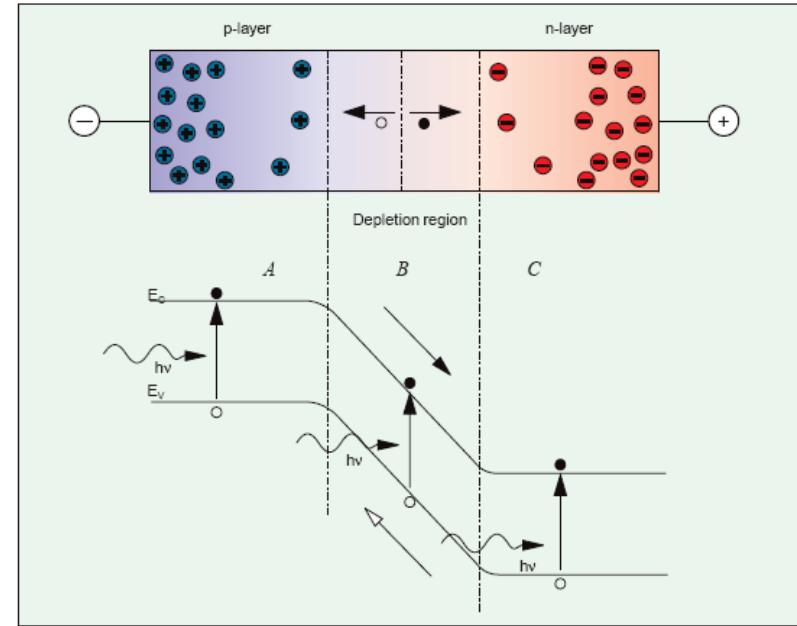
- eficienta crescuta a conversiei optic/electric
- zgomot redus
- raspuns uniform la diferite lungimi de unda
- viteza de raspuns ridicata
- liniaritate

► Principii de operare

- fotoconductori $R = R(P_o)$
- fototranzistori $I_B = I_B(P_o)$
- fotodiode $I = I(P_o)$
 - pn
 - pin
 - pin cu multiplicare in avalansa
 - Schottky

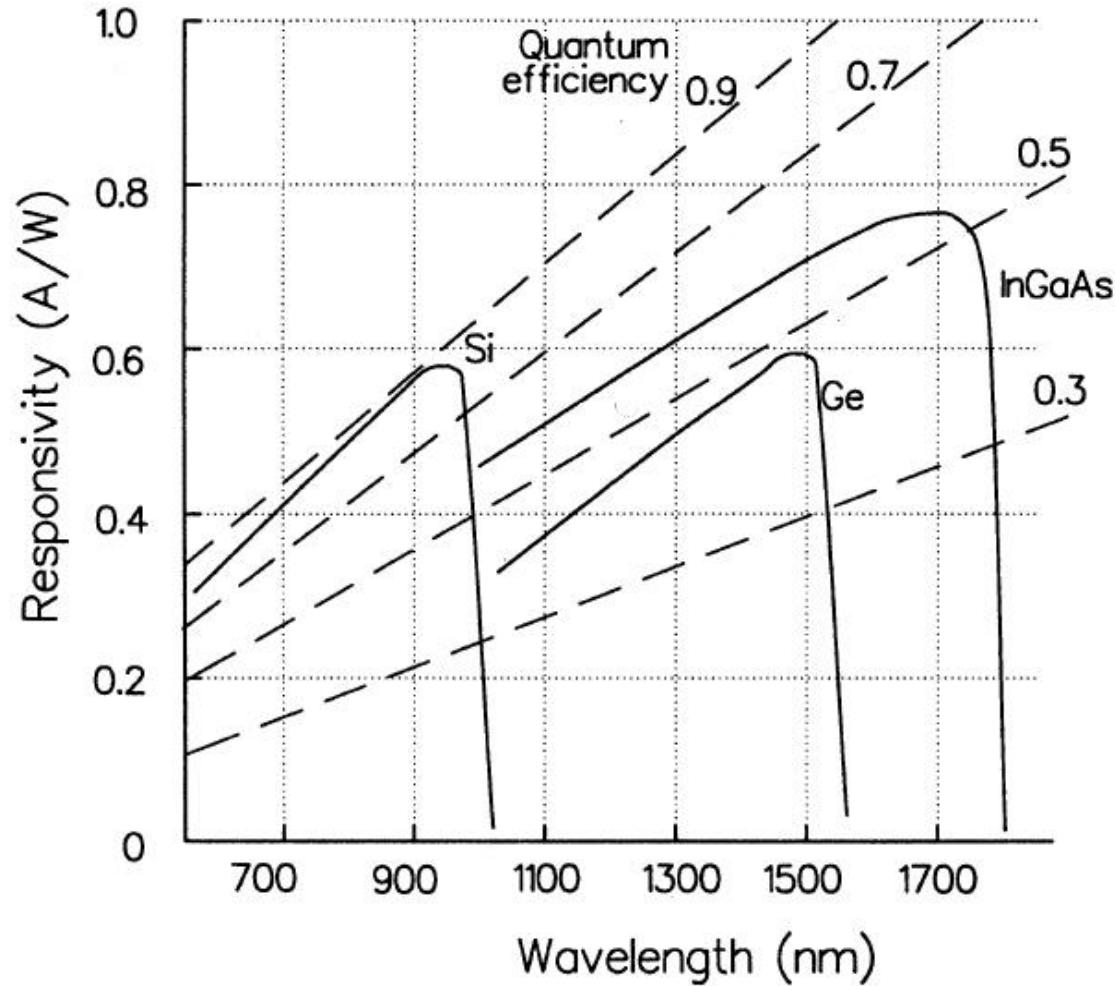
Fotodioda – Principiul de operare

- ▶ Jonctiunea pn este polarizata invers
- ▶ Lumina este absorbita in regiunea golita de purtatori, un foton absorbit generand o pereche electron-gol
- ▶ Sarcinile sunt separate de campul electric existent in regiunea golita si genereaza un curent in circuitul exterior



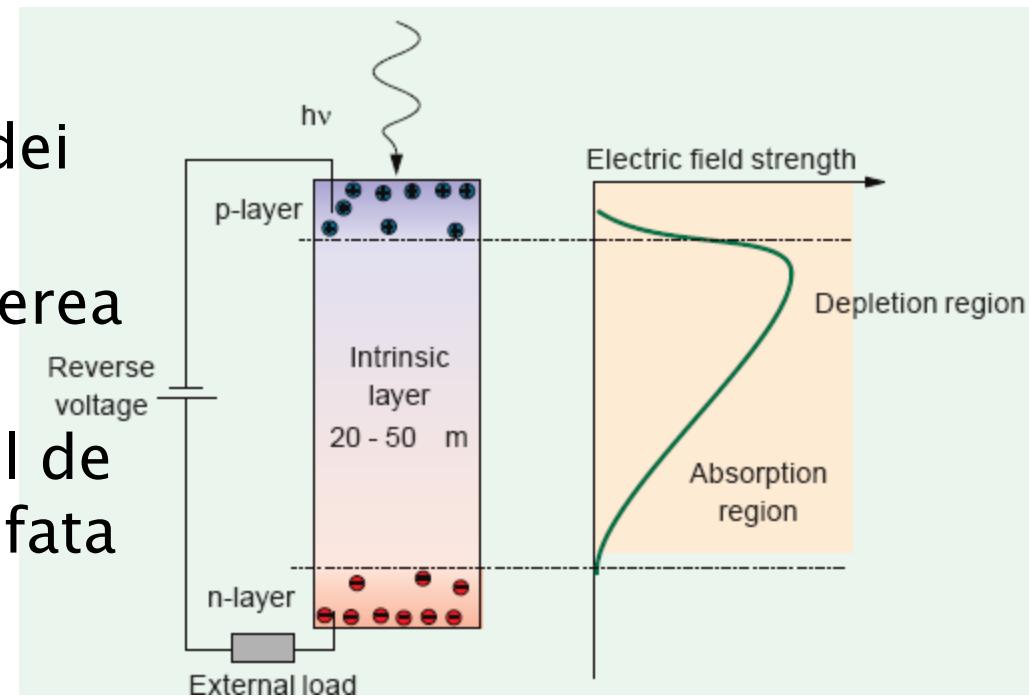
Fotodiode – marimi karakteristice

$$R = \frac{I}{P_o} = \eta \cdot \frac{e}{hc} \cdot \lambda$$



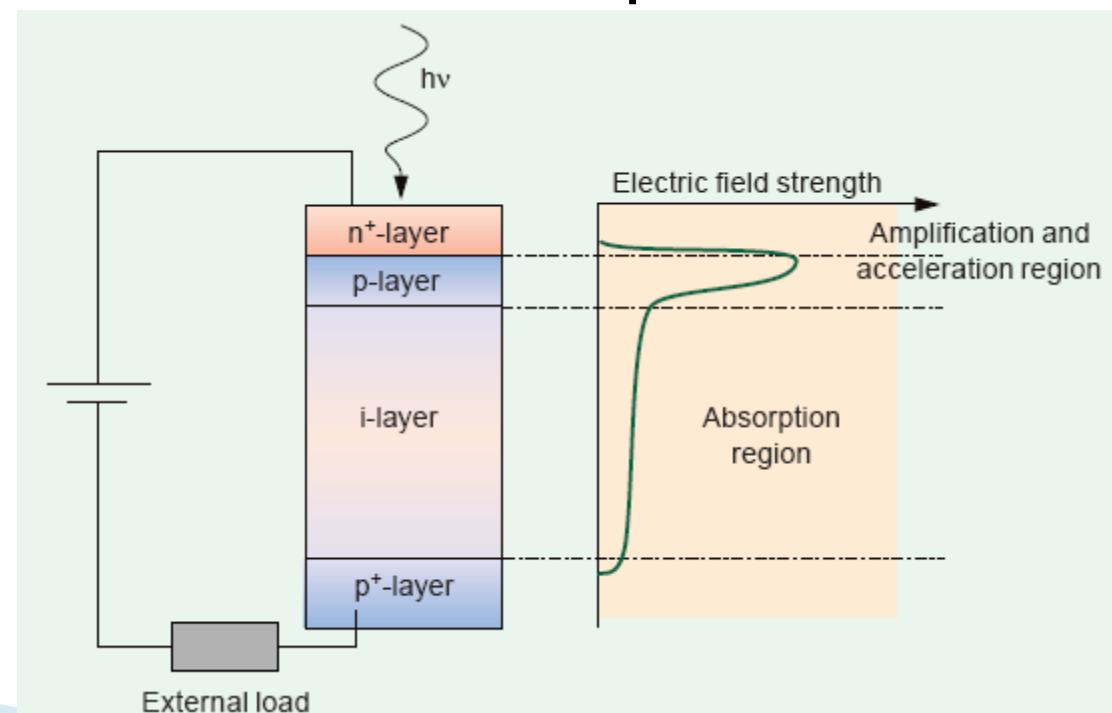
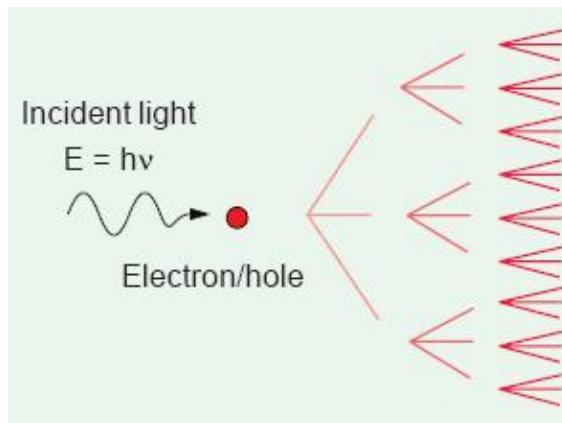
Fotodioda PIN

- ▶ Solutia consta in introducerea unui strat foarte slab dopat (intrinsec) intre cele doua zone ale diodei
 - creste volumul de absorbtie deci creste sensibilitatea fotodiodei
 - capacitatea jonctiunii scade ducand la cresterea vitezei
 - este favorizat curentul de conductie (mai rapid) fata de cel de difuzie



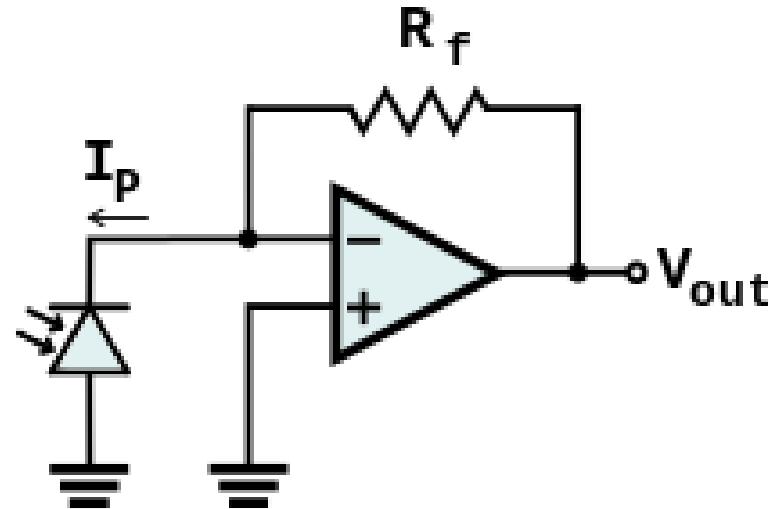
Fotodioda PIN cu multiplicare in avalansa

- ▶ daca viteza purtatorilor este suficient de mare genereaza noi perechi electron/gol prin ionizare de impact
- ▶ amplificarea are loc in acelasi timp cu detectia



Amplificatoare transimpedanta

- ▶ Trebuie realizat un compromis intre
 - zgomot
 - castig
 - viteza
- ▶ De obicei sunt realizate cu reactie



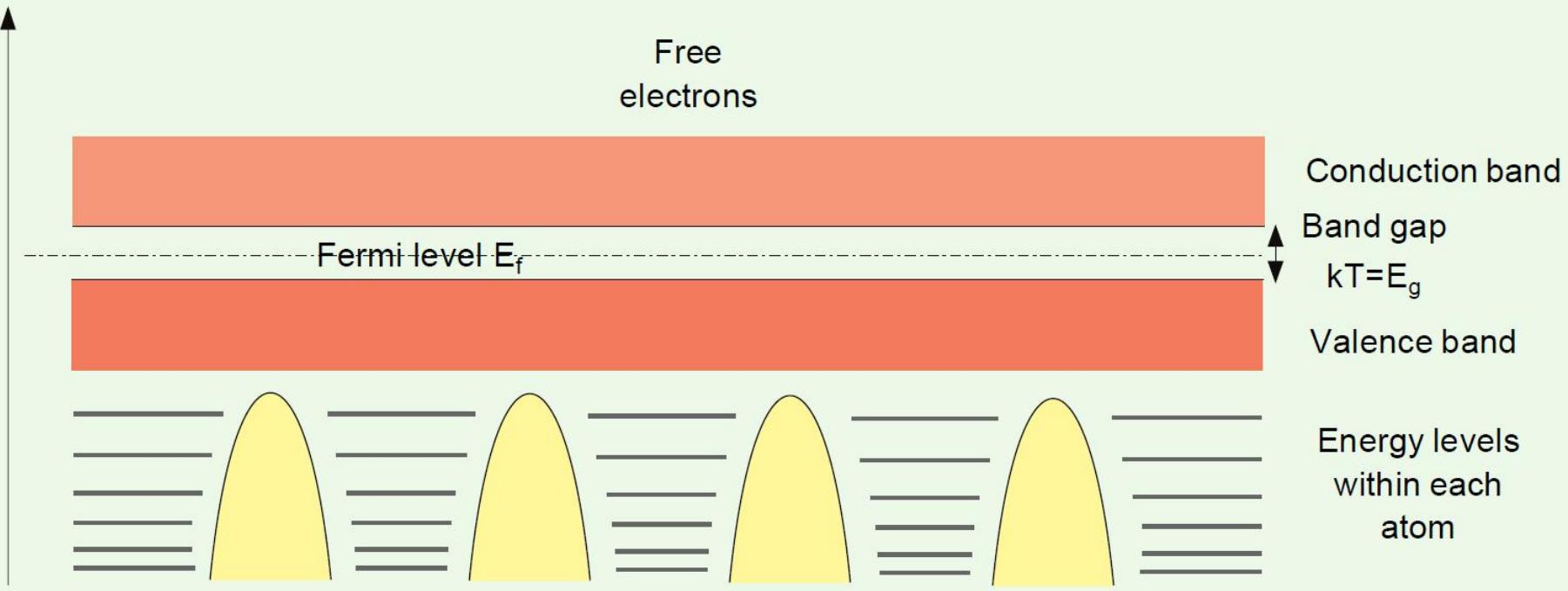
Utilizare celule solare

Capitolul 9

Efect fotovoltaic

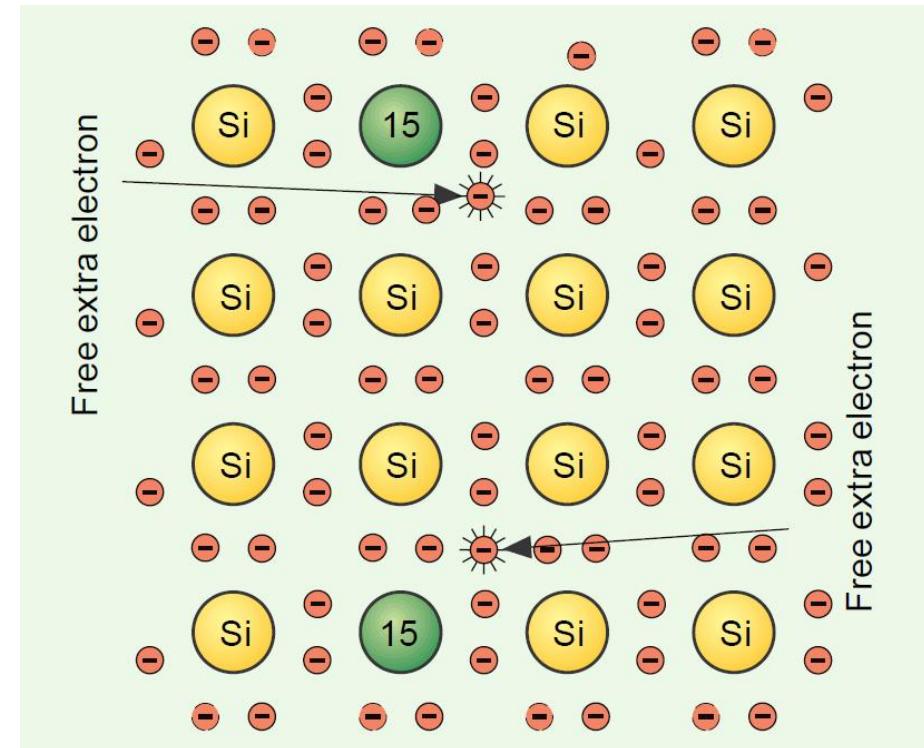
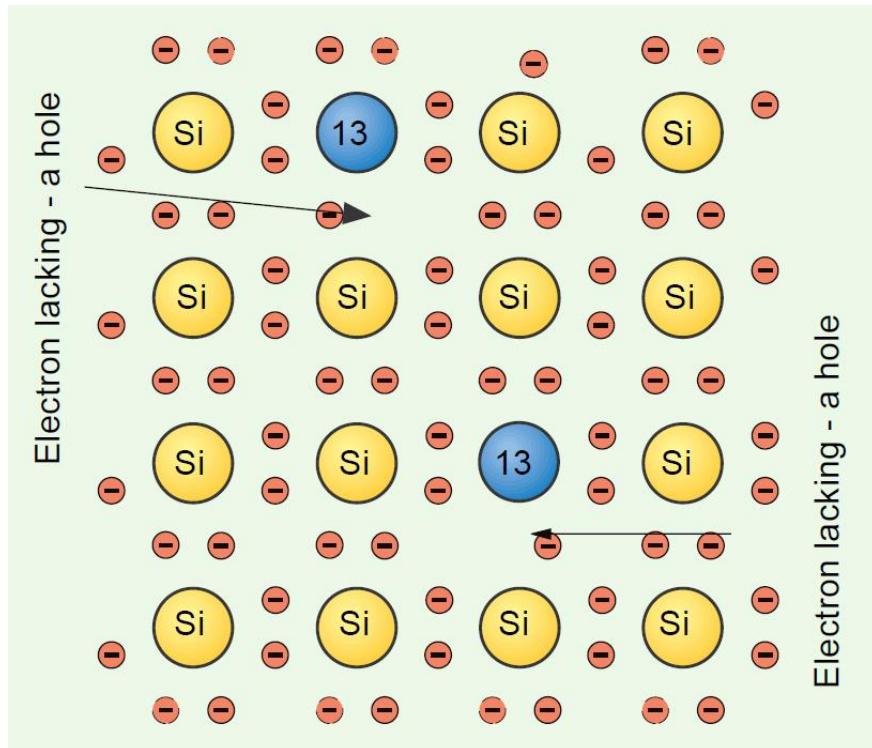
▶ joncțiunea pn

Energy level



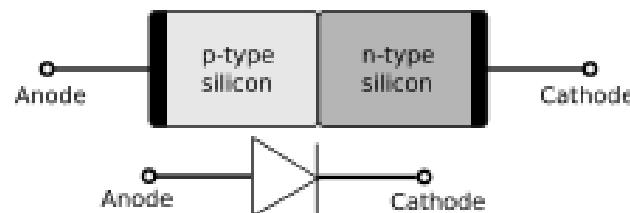
Efect fotovoltaic

► joncțiunea pn

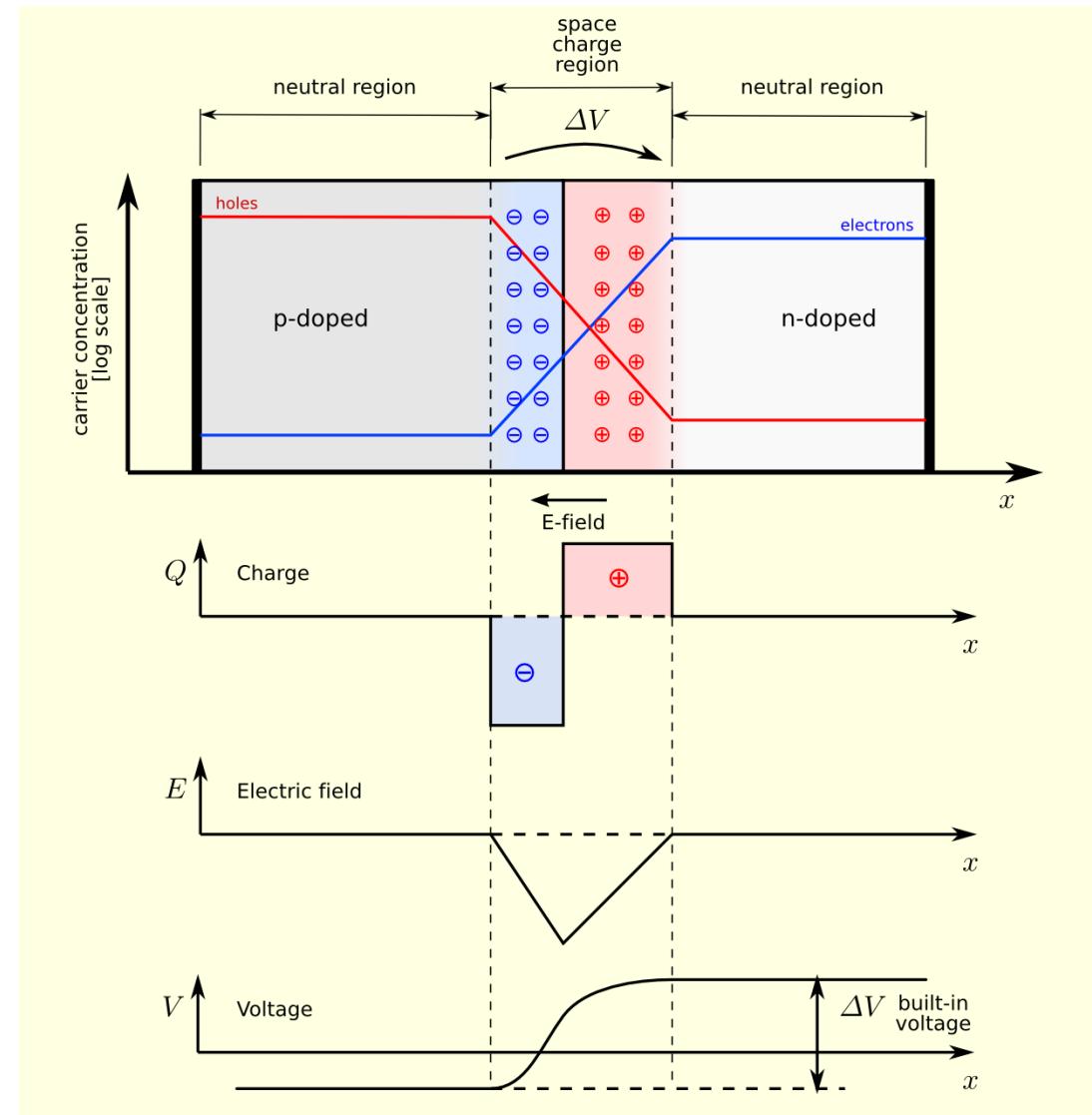


Efect fotovoltaic

▶ joncțiunea pn

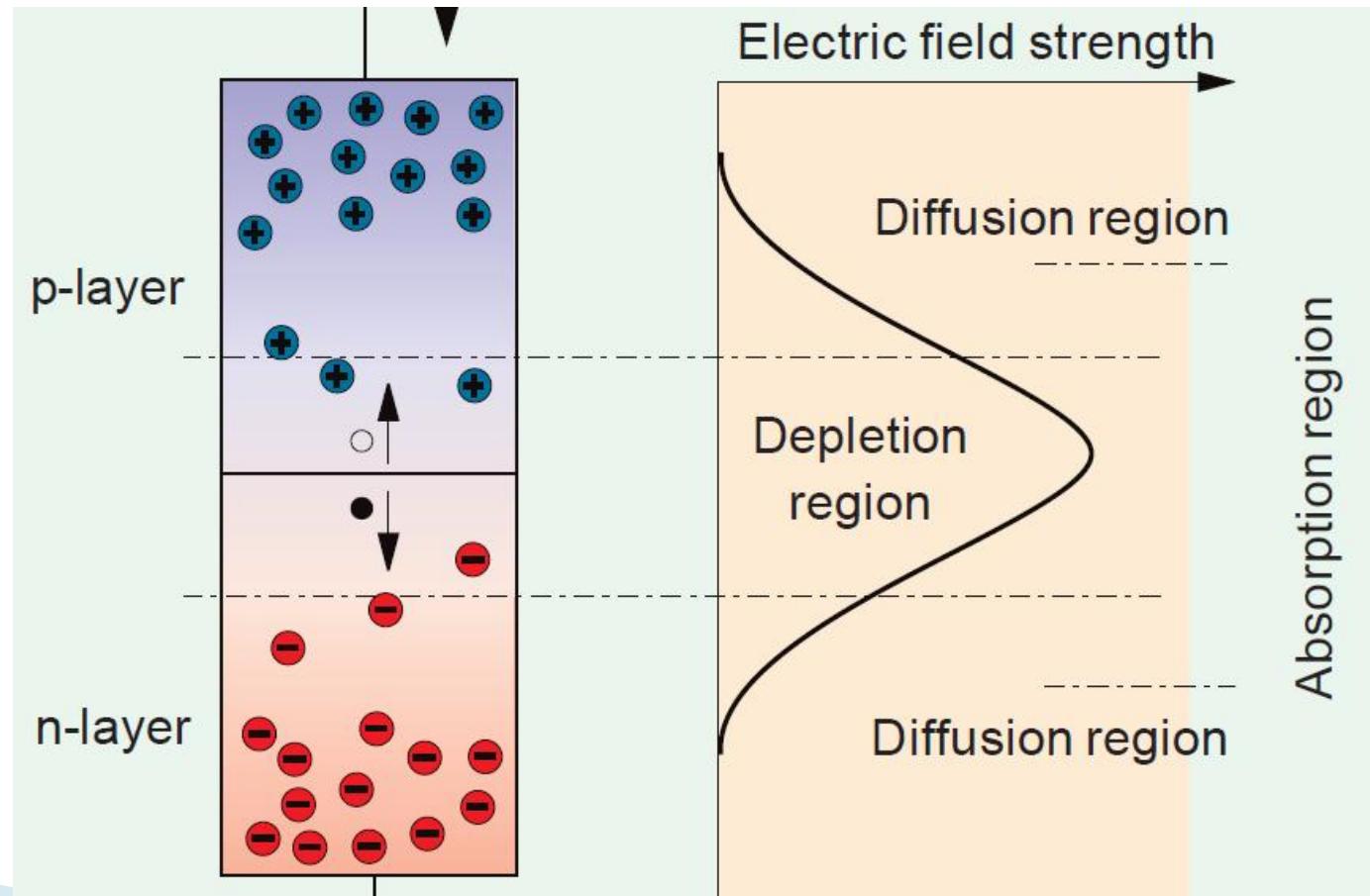


$$V > V_D$$



Efect fotovoltaic

▶ joncțiunea pn / Fotodioda

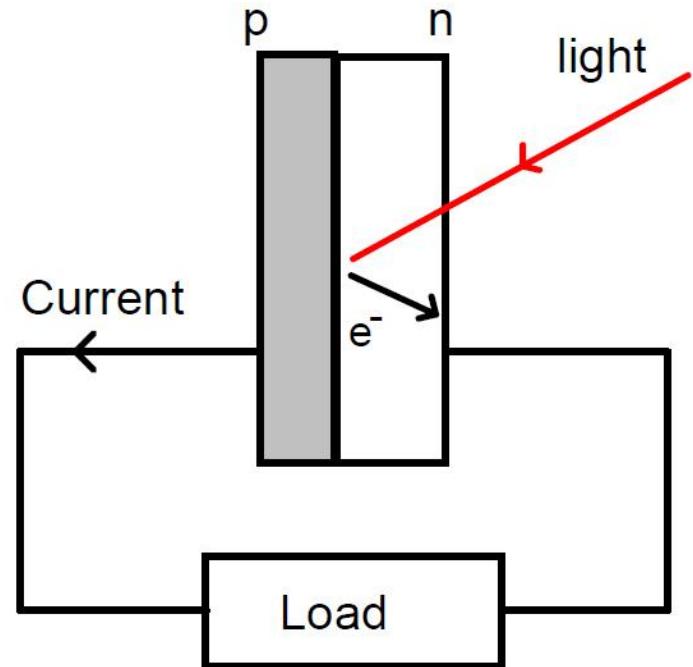
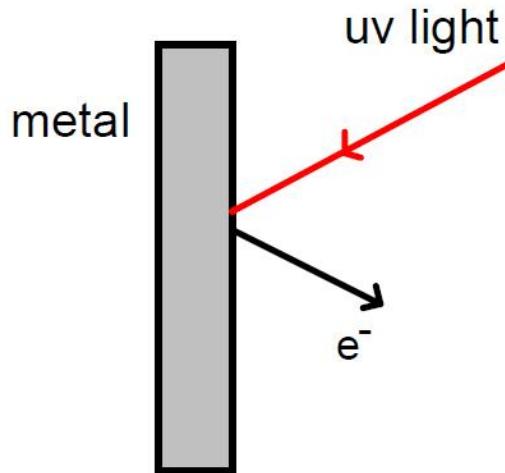


Efect fotovoltaic

- ▶ generarea unei perechi electron/gol in interiorul unui material prin absorbtia energiei fotonilor incidenti si cresterea energiei potentiiale a electronilor
 - urmat de posibilitatea separarii sarcinilor
- ▶ deosebit de conversia:
 - fototermica (energia fotonilor este convertita in caldura – energie cinetica a electronilor)
 - fotochimica (fotosinteza energie potentiala utilizata chimic)
- ▶ duce la aparitia unei tensiuni electromotoare si a unui curent intr-un circuit inchis

Efect fotovoltaic

- ▶ diferit de efectul fotoelectric (cu toate ca este asemanator ca principiu)

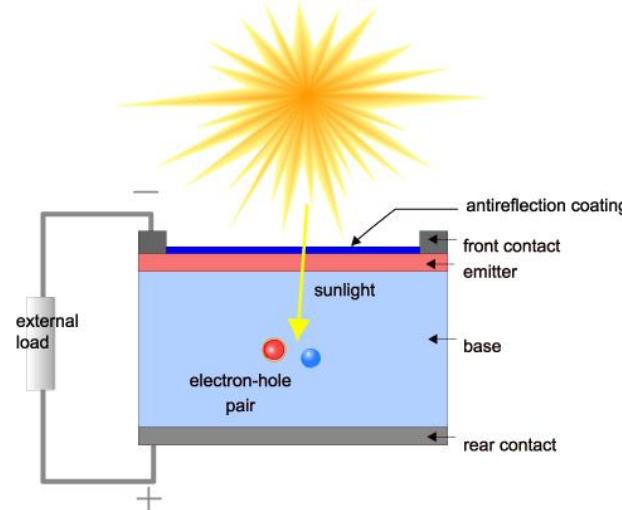


Efect fotovoltaic

- ▶ Separarea fizica a sarcinilor este de obicei realizata prin utilizarea unei jonctiuni pn:
 - campul electric generat de distributia sarcinilor in zona golita de portatori a jonctiunii
- ▶ In principiu o **celula solară** este o **fotodiode** in care:
 - nivelul de semnal optic este ridicat (fortarea prin polarizare inversa externa a extragerii tuturor electronilor generati nu e necesara)
 - viteza de lucru nu e importanta (accelerarea iesirii din dispozitiv a electronilor generati nu e necesara)

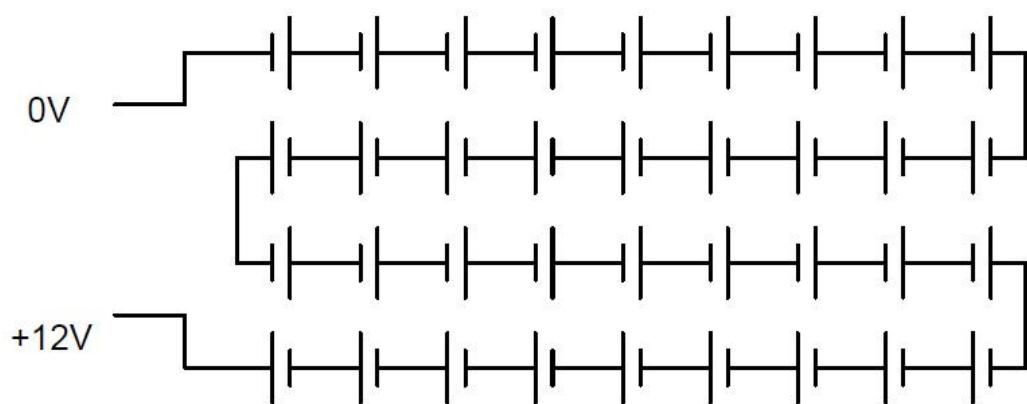
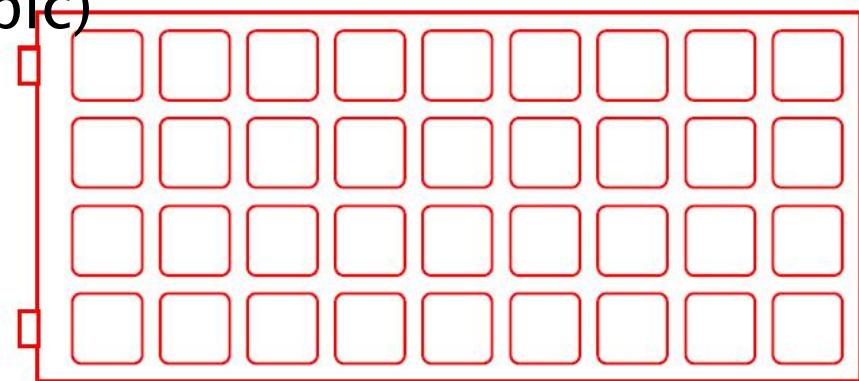
Celula solară (fotovoltaica)

- ▶ în principiu o dioda
 - cu arie mare ($\sim 100\text{cm}^2$)
 - cu suprafață tratată antireflectorizant
 - generează o tensiune electromotoare de $0.5\div 1\text{V}$
 - generează curenti de scurtcircuit de $\times 0 \text{ mA/cm}^2$



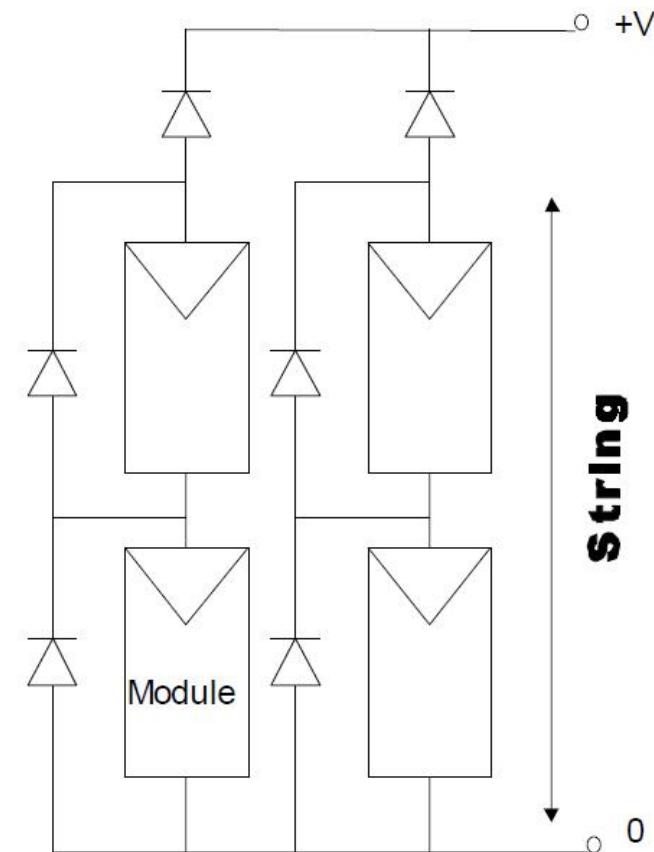
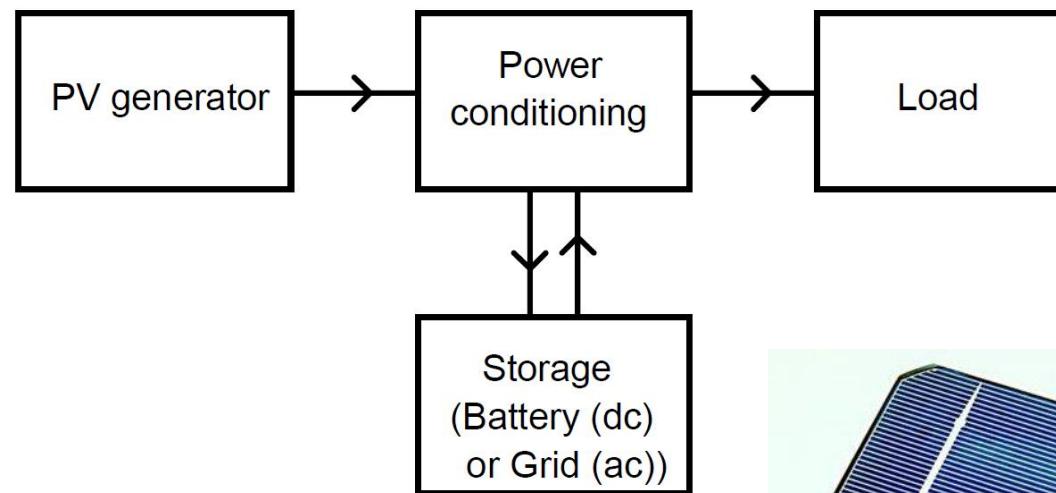
Celula solară (fotovoltaica)

- ▶ pentru utilizare în practică
 - module de 28 – 36 de celule conectate în serie
 - crește tensiunea la 12V (tipic)



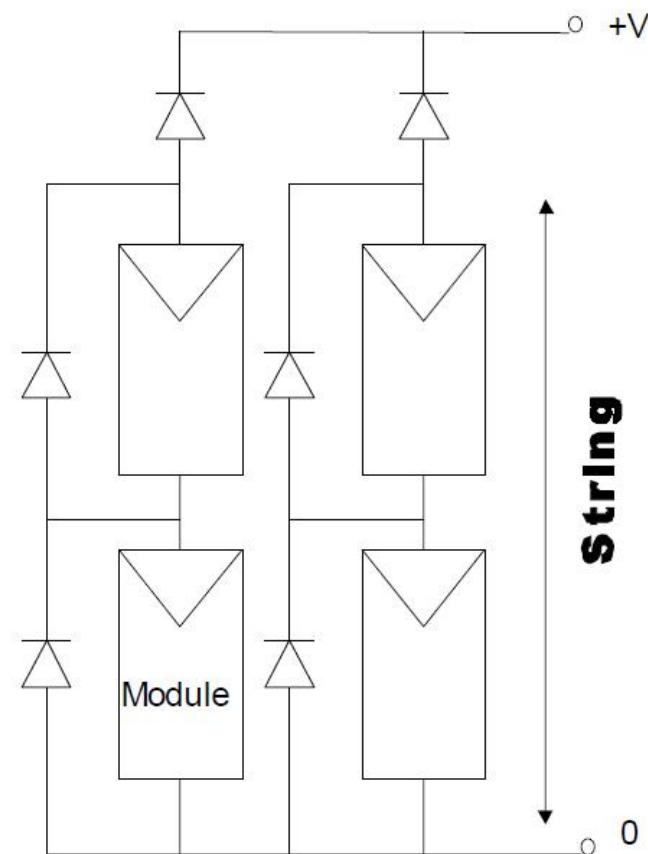
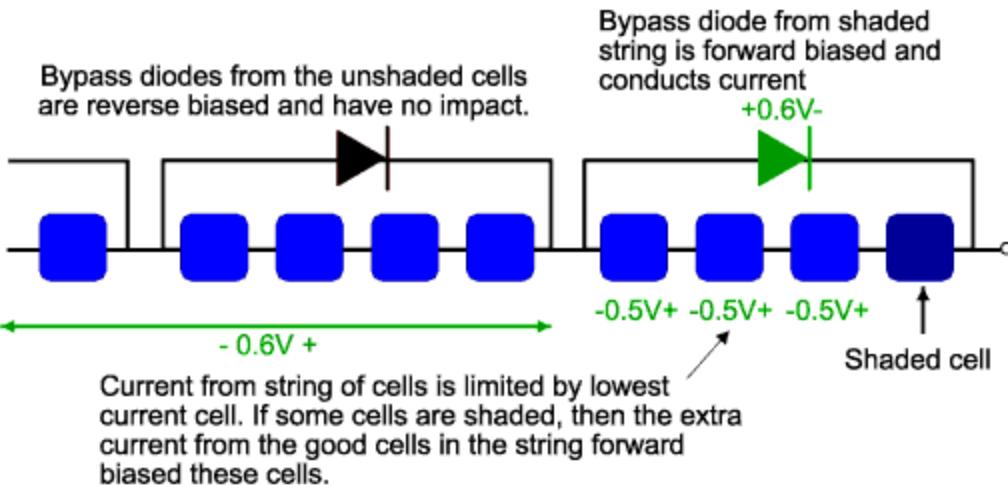
Celula solară (fotovoltaica)

- ▶ pentru utilizare în practică
 - modulele sunt conectate în serie și/sau paralel pentru obținerea tensiunilor/curenților necesari pentru aplicatie



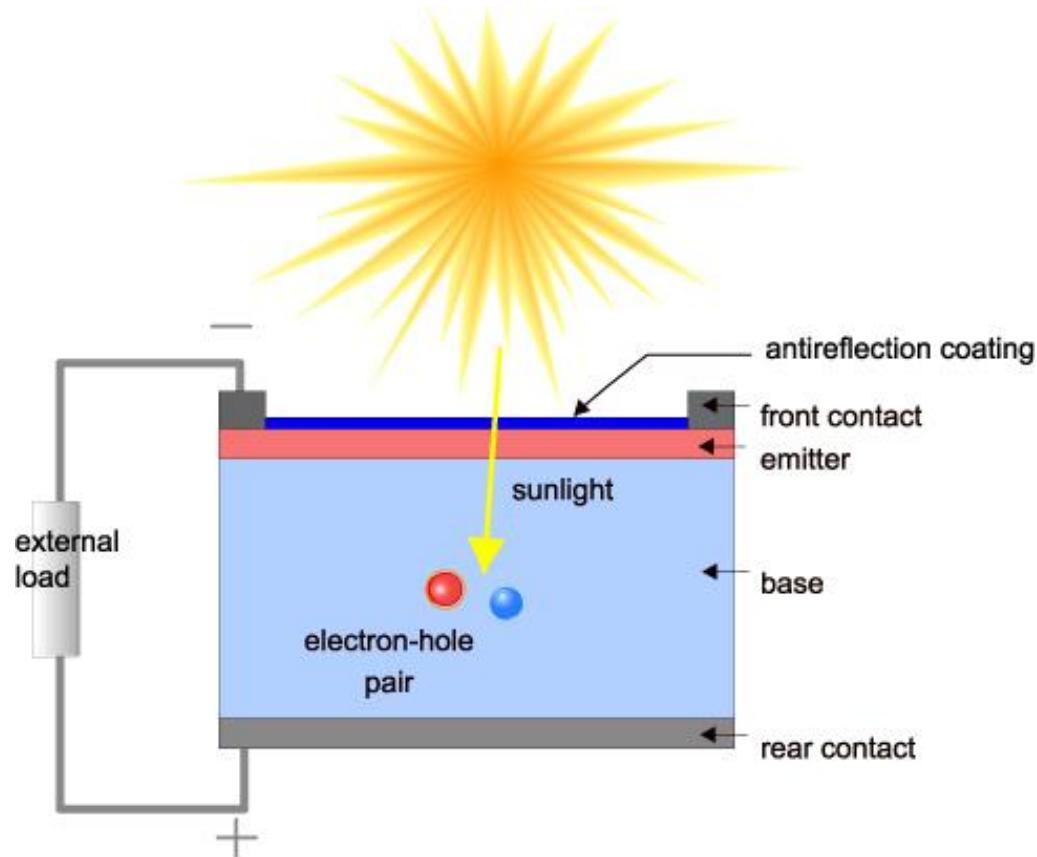
Celula solară (fotovoltaica)

- ▶ pentru utilizare in practica
 - diode pentru flexibilitate



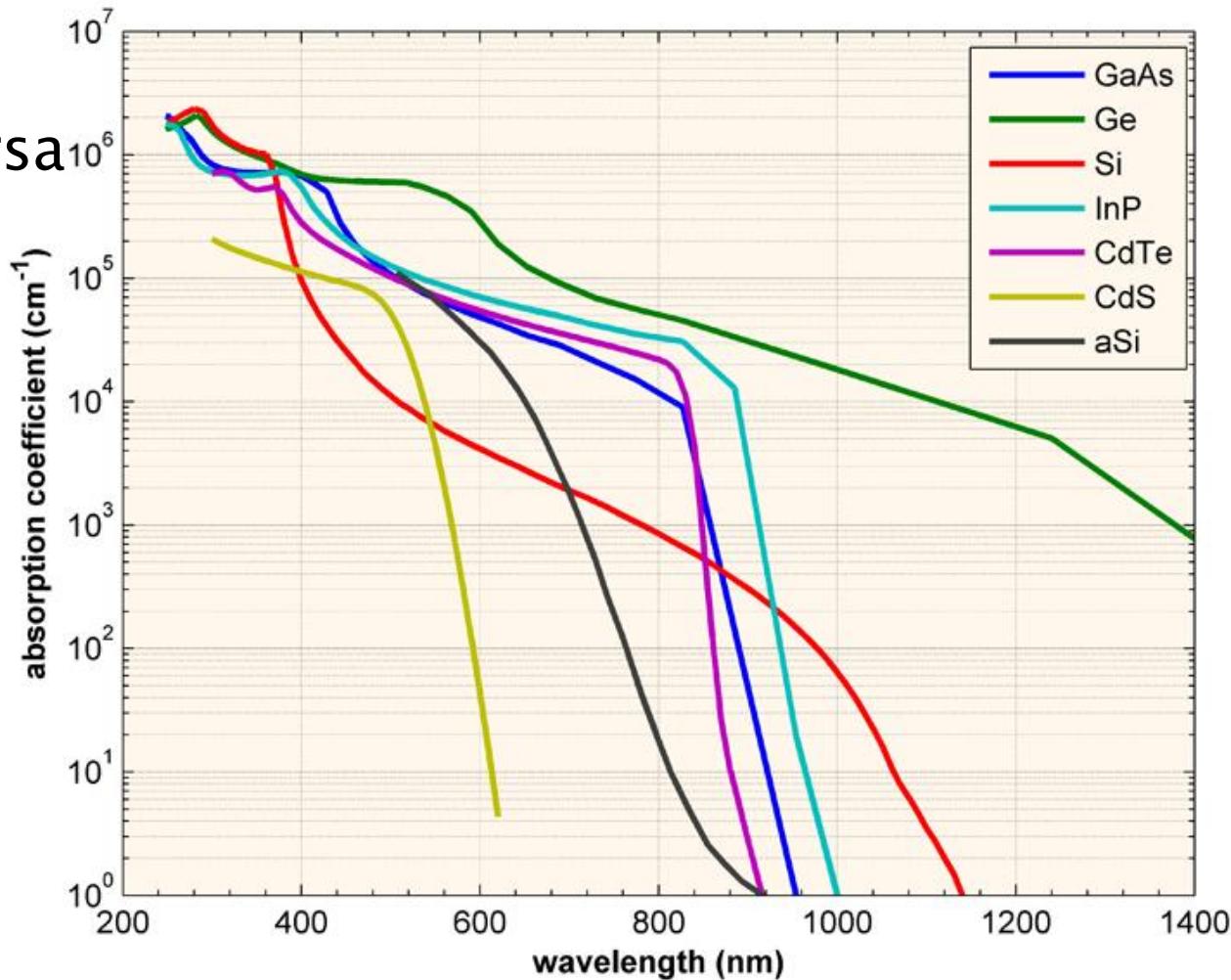
Celula solară (fotovoltaica)

- ▶ în principiu o dioda



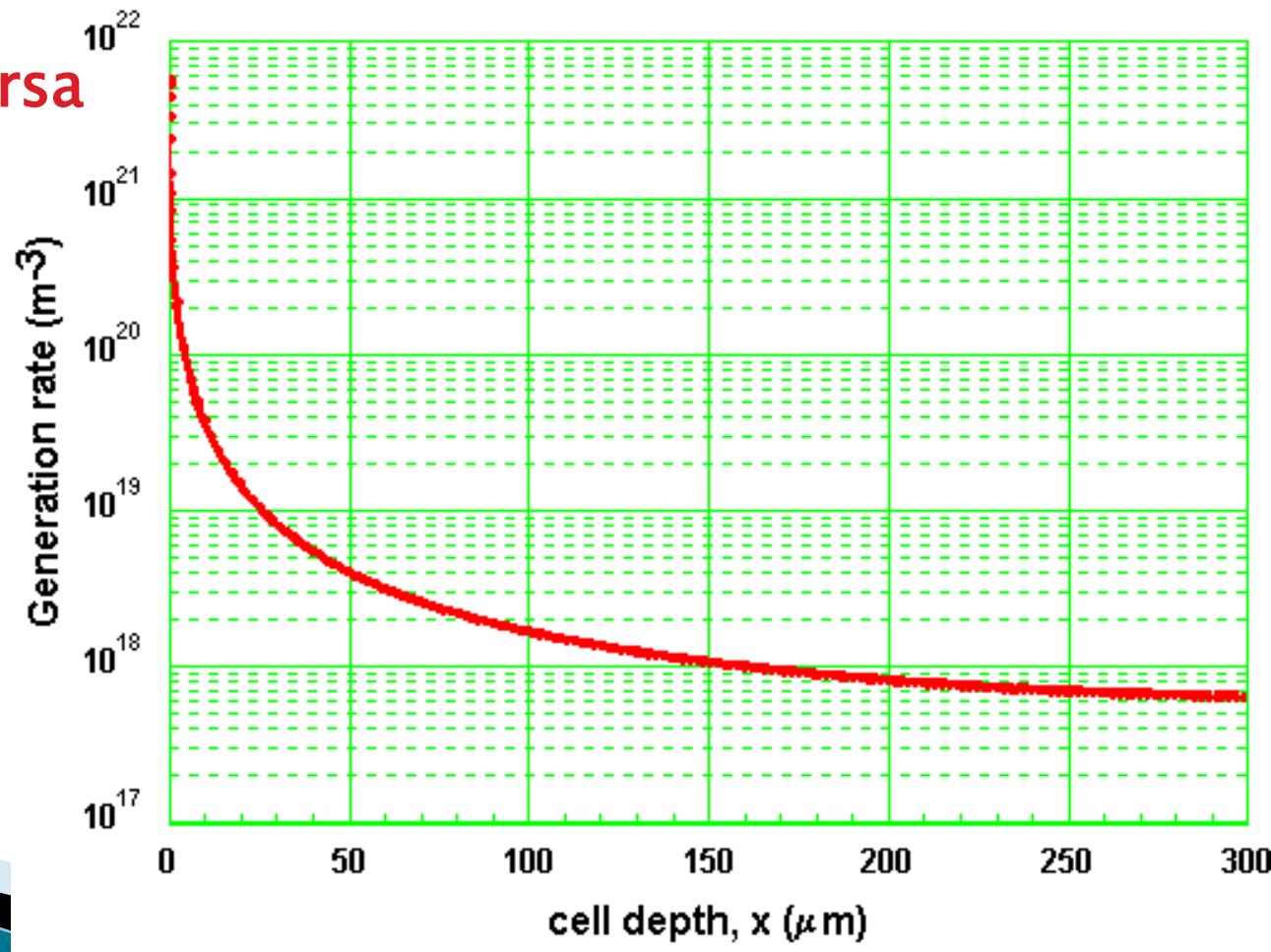
Celula solară

- ▶ probabilitate de generare a purtătorilor depinde de
 - **material**
 - distanța parcursă



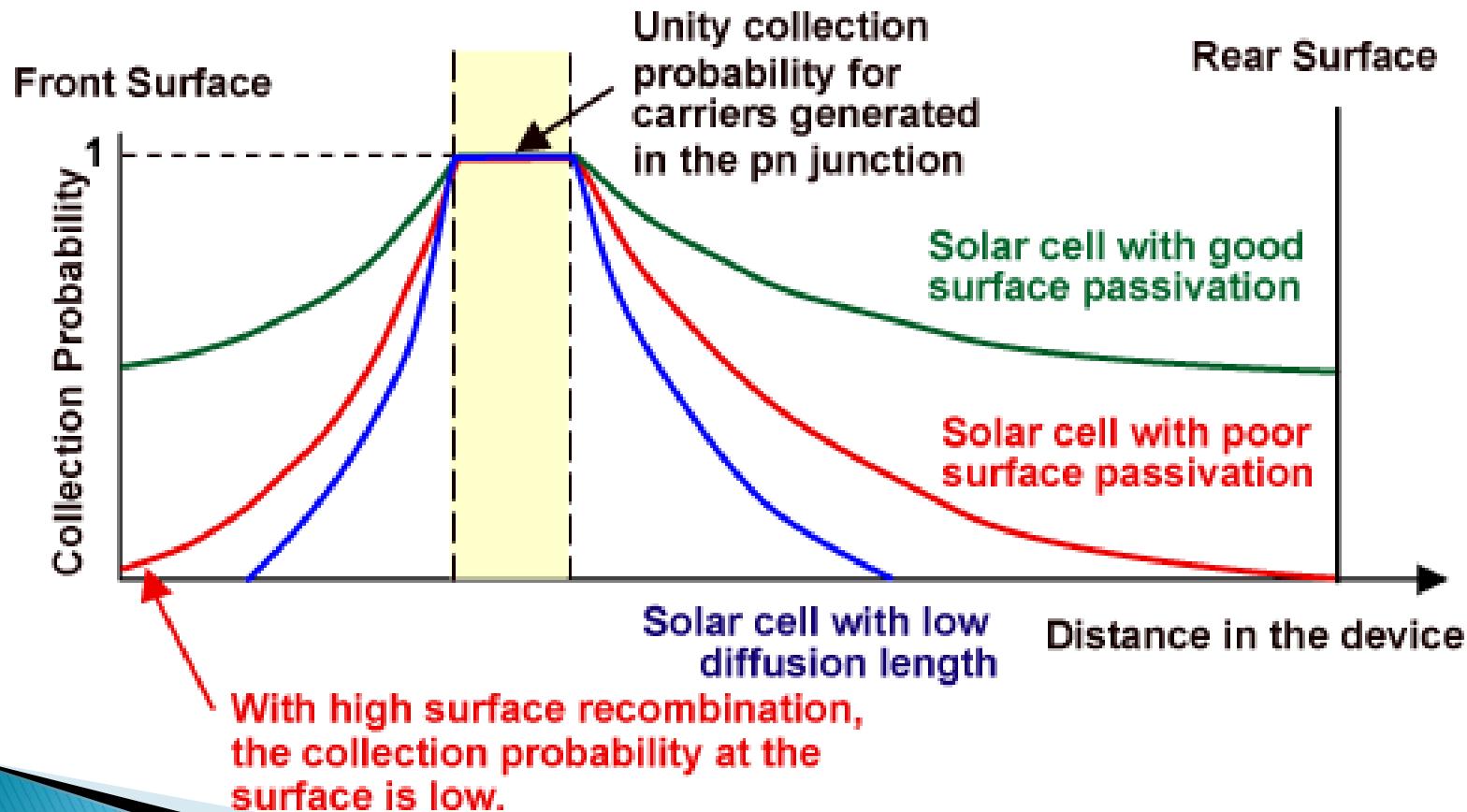
Celula solara

- ▶ probabilitate de generare a purtatorilor depinde de
 - material
 - **distanța parcursă**



Celula solara

- ▶ probabilitate de captura a purtatorilor



Celula solară/Fotodioda

- ▶ Energia necesara pentru eliberarea unei perechi electron gol

$$h\nu = \frac{hc}{\lambda} \geq E_g$$

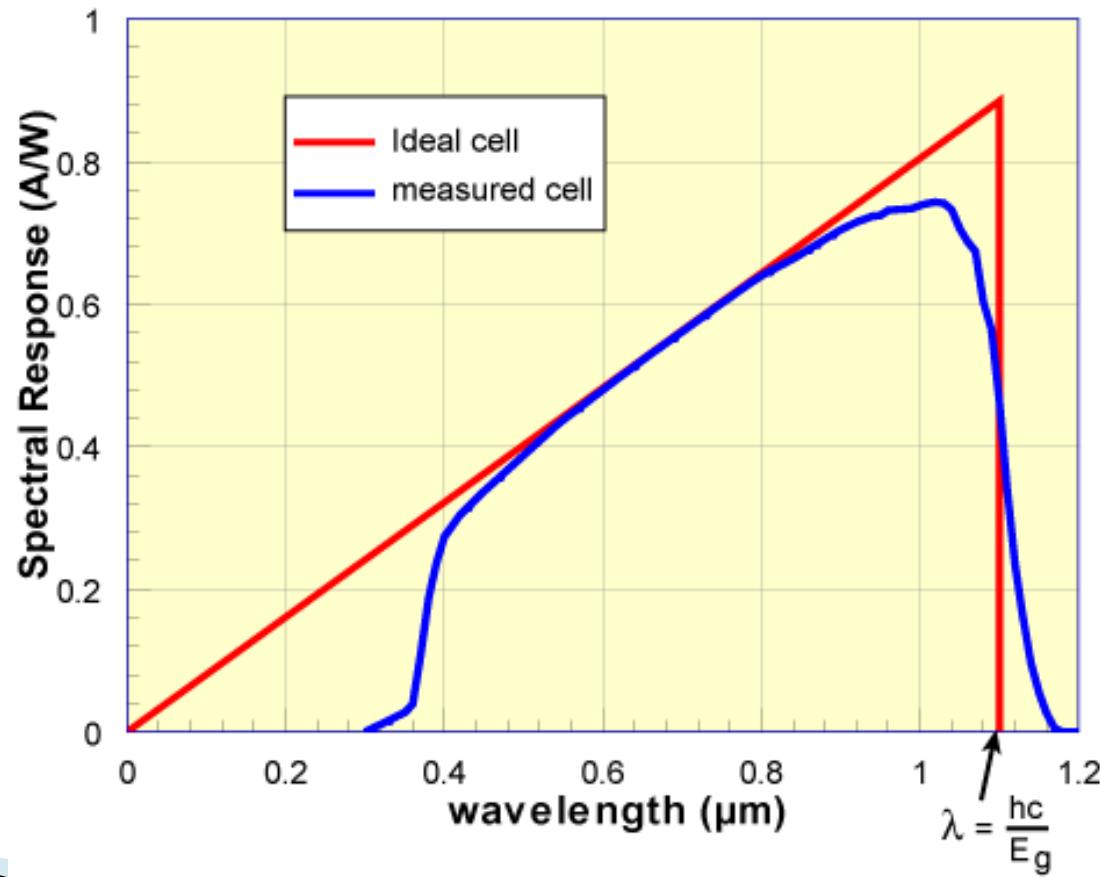
- ▶ Lungime de undă de taiere

$$\lambda_{\max} = \frac{hc}{E_g}$$

- ▶ Coeficientul de absorbtie are valoare mare la lungimi de undă reduse
- ▶ Ca urmare comportarea **tuturor** materialelor este de tip trece banda

Celula solară

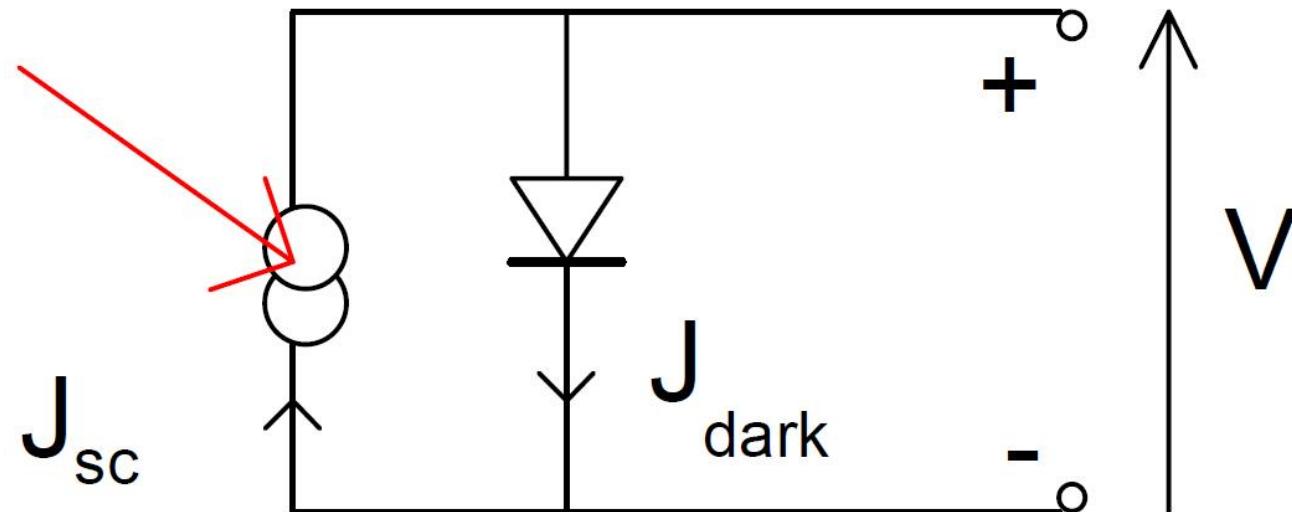
- ▶ raspuns spectral



Celula solara

▶ Schema echivalenta

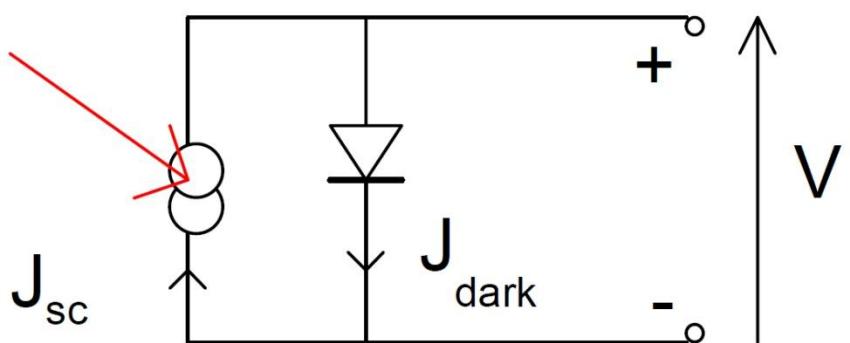
- dioda
- sursa de curent generat de fluxul de fotoni incident



Celula solara

▶ Schema echivalenta

- dioda
- sursa de curent generat de iluminarea energetica incidenta
 - curent de intuneric



$$I_d(V) = I_0 \cdot (e^{eV/KT} - 1)$$

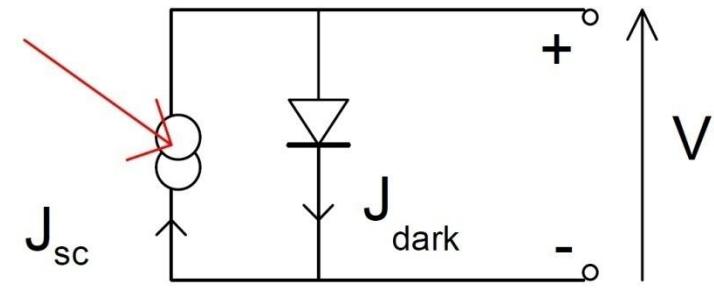
- adaugarea curentului generat de fotoni

$$I(E_e, V) = I_{sc}(E_e) - I_d(V)$$

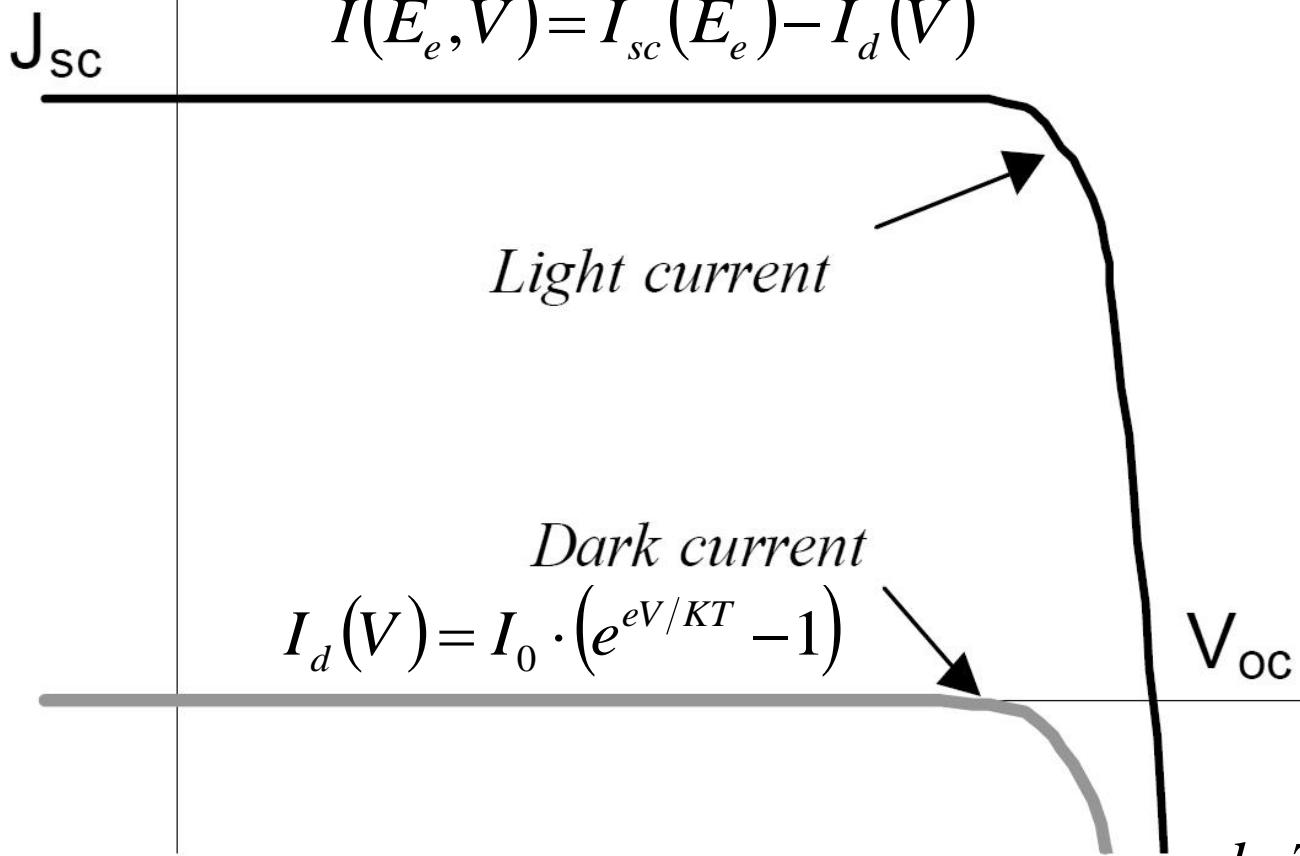
- tensiunea in gol

$$V_{oc} = \frac{k \cdot T}{e} \cdot \ln \left(\frac{I_{sc}(E_e)}{I_0} - 1 \right)$$

Celula solară



$$I(E_e, V) = I_{sc}(E_e) - I_d(V)$$



Dark current

$$I_d(V) = I_0 \cdot (e^{eV/KT} - 1)$$

Bias voltage, V

$$V_{oc} = \frac{k \cdot T}{e} \cdot \ln \left(\frac{I_{sc}(E_e)}{I_0} - 1 \right)$$

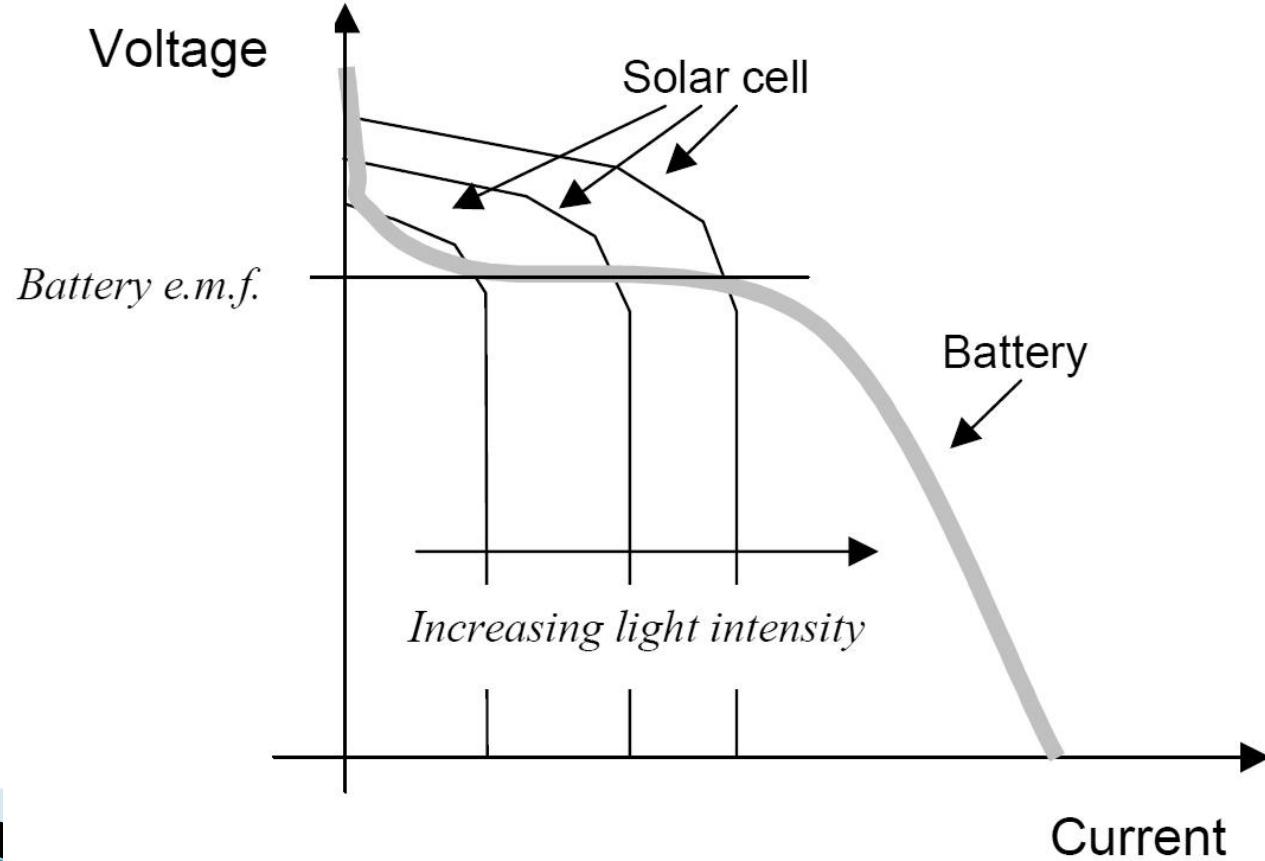
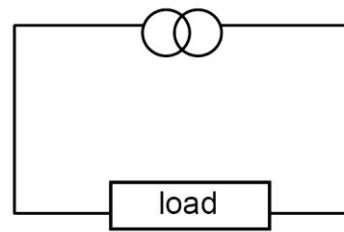
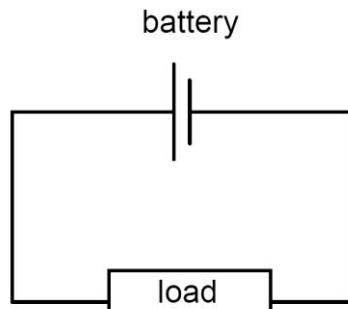
V_{oc}

Light current

Current density, J

Celula solara

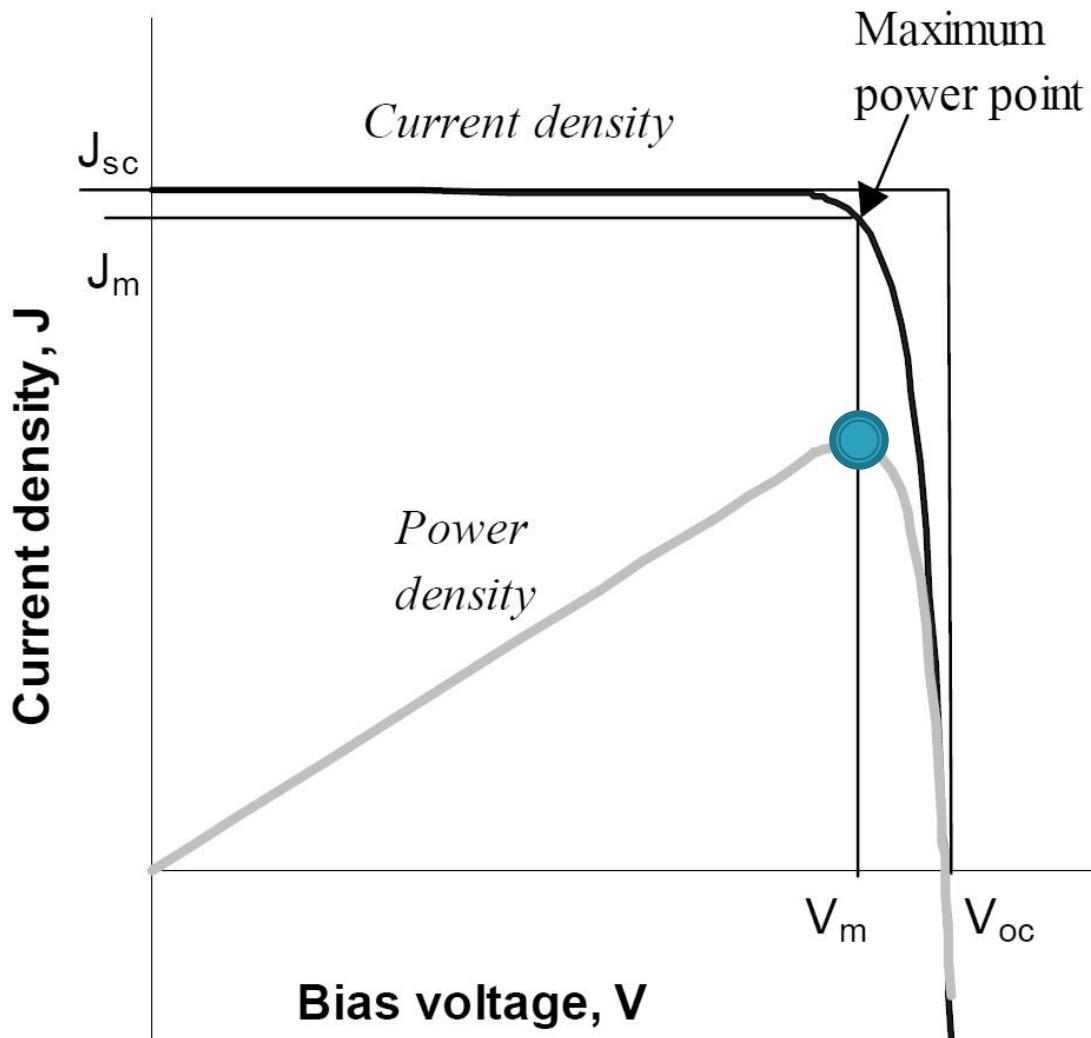
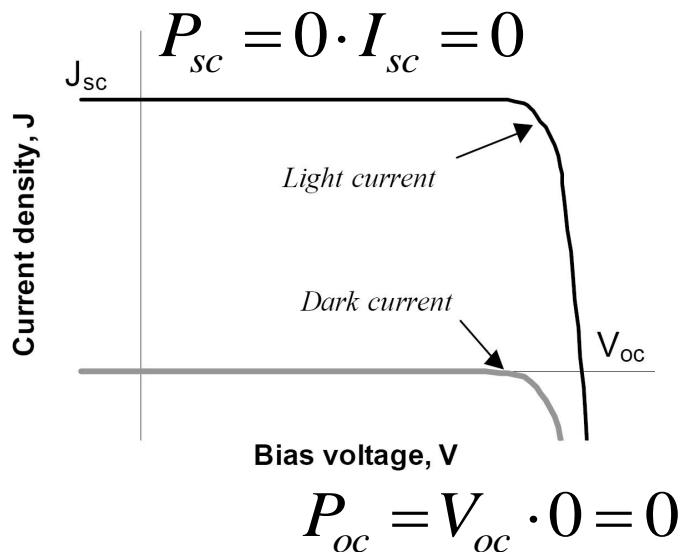
- ▶ poate fi folosita in loc de baterie intr-un circuit electric
 - cu anumite diferente



Celula solară

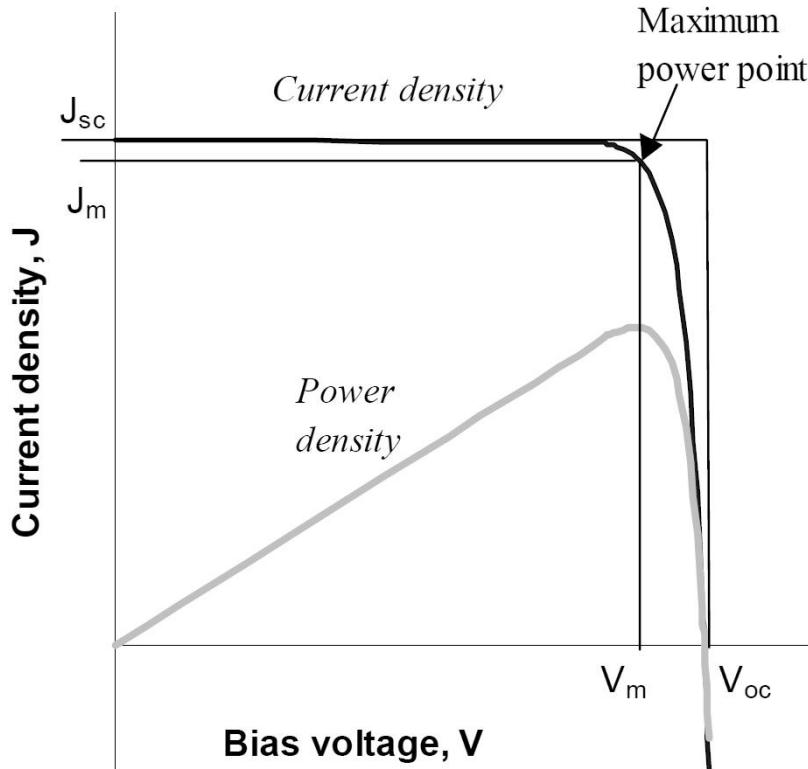
▶ Putere generată

$$P = V \cdot I$$



Celula solara

▶ Putere generata



$$P_m = V_{pm} \cdot I_{pm}$$

▶ Valorile de curent si tensiune pentru putere maxima sunt date de catalog, circuitul de conditionare care urmeaza dupa celule poate fi **optimizat** sa functioneze la aceste valori

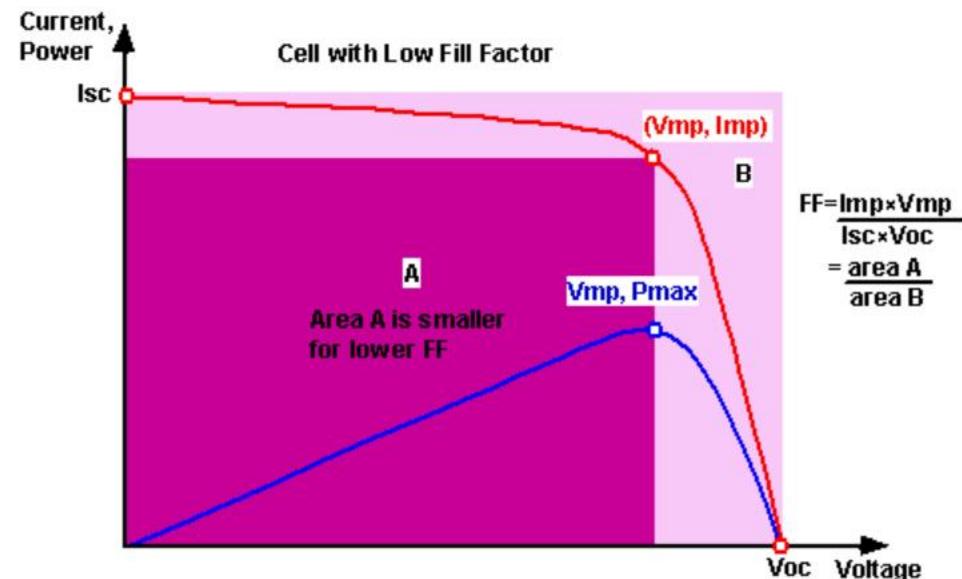
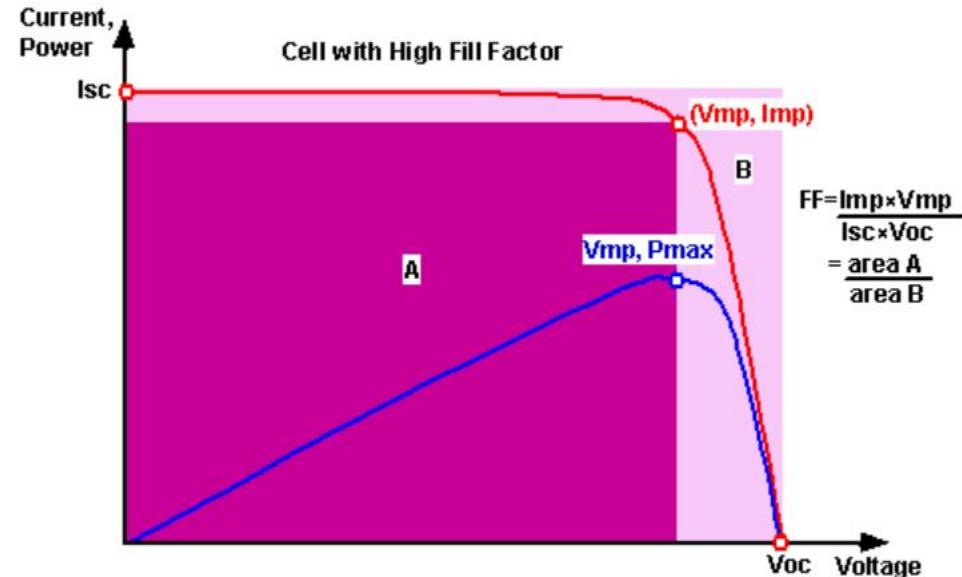
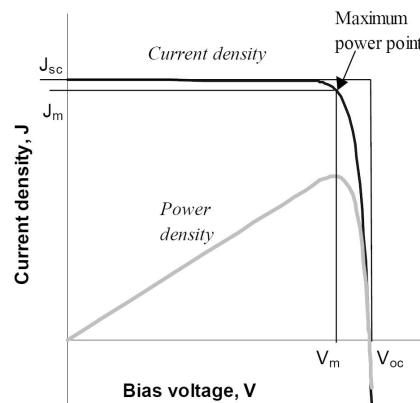
Celula solară

- Factor de umplere

$$FF = \frac{V_{pm} \cdot I_{pm}}{V_{oc} \cdot I_{sc}}$$

- o masură a calității celulei
 - dependent de material

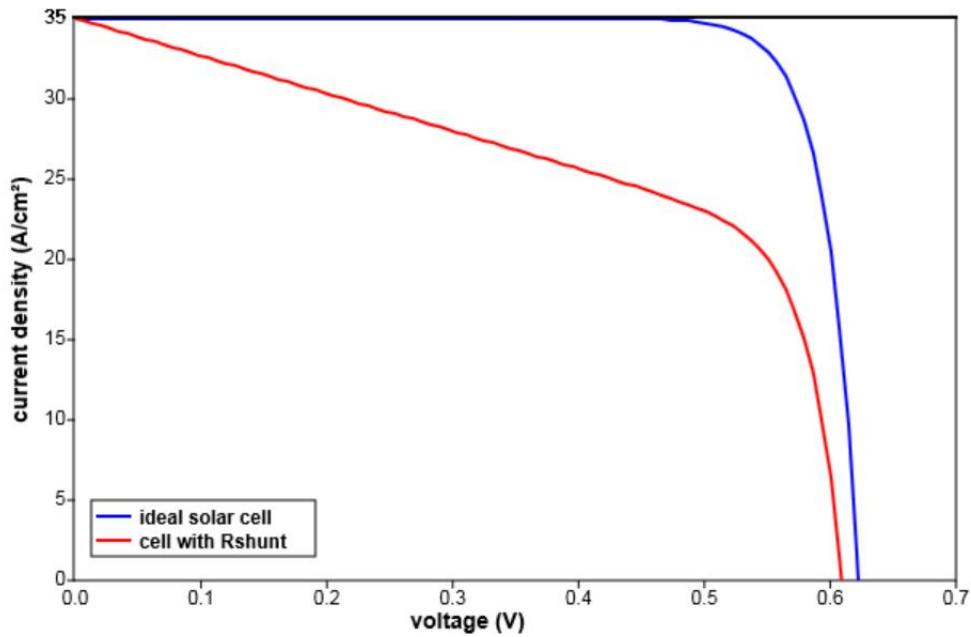
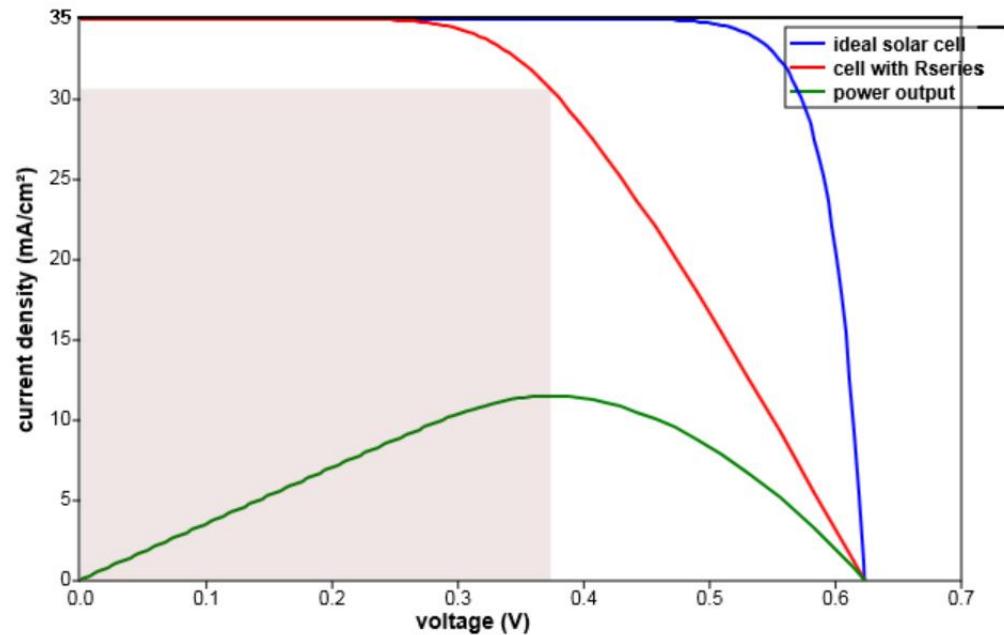
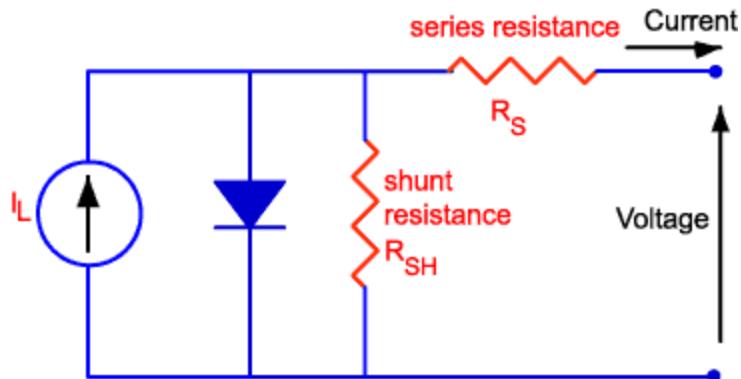
$$P_m = V_{pm} \cdot I_{pm}$$



Efect pierderi

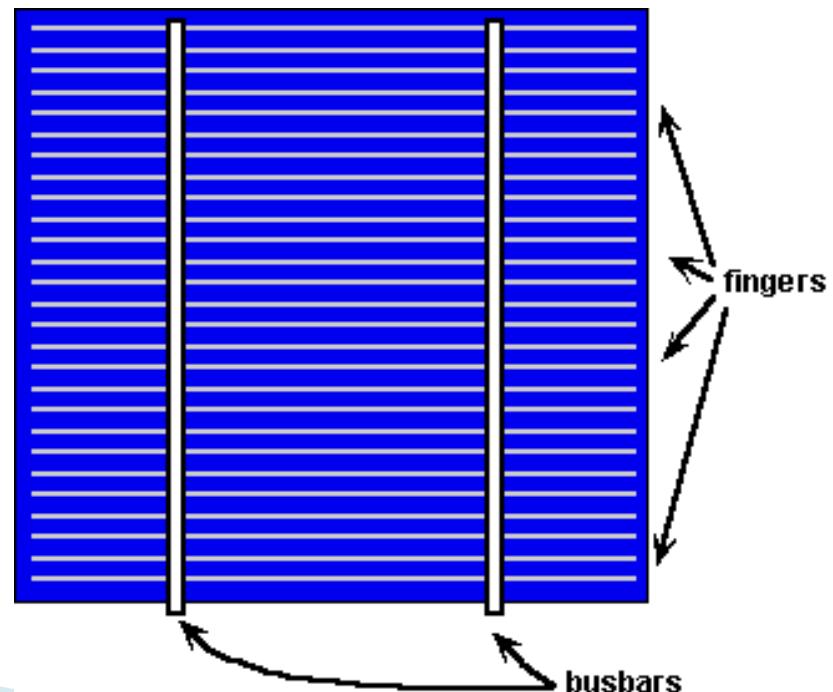
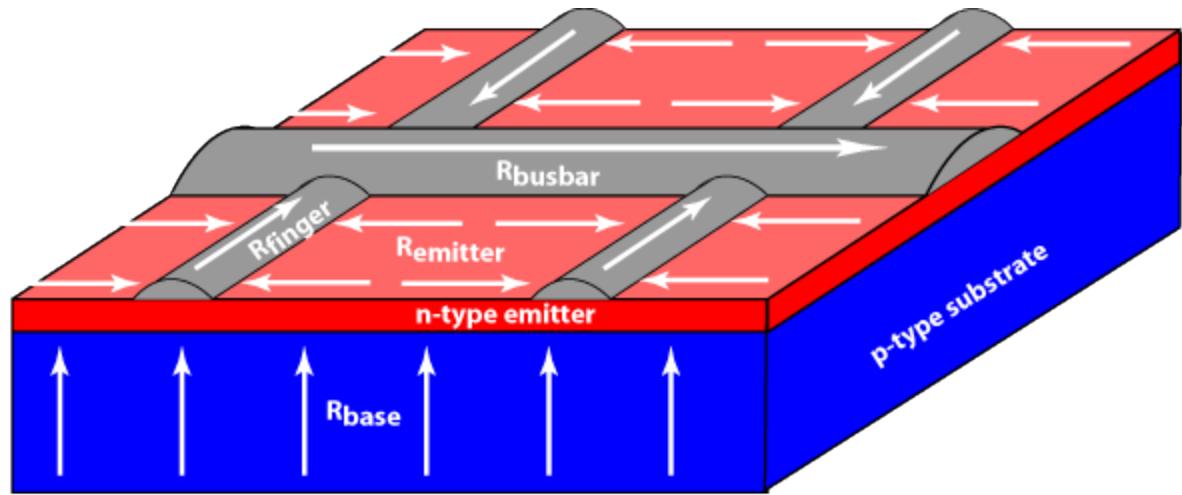
- ▶ Rezistenta serie
 - rezistenta echivalenta a semiconductorului utilizat
 - rezistenta jonctiunilor metal/semiconductor
 - rezistenta contactului metalic al anodului si colectorului
- ▶ Rezistenta paralel
 - generata de defecte de fabricatie

Efect pierderi



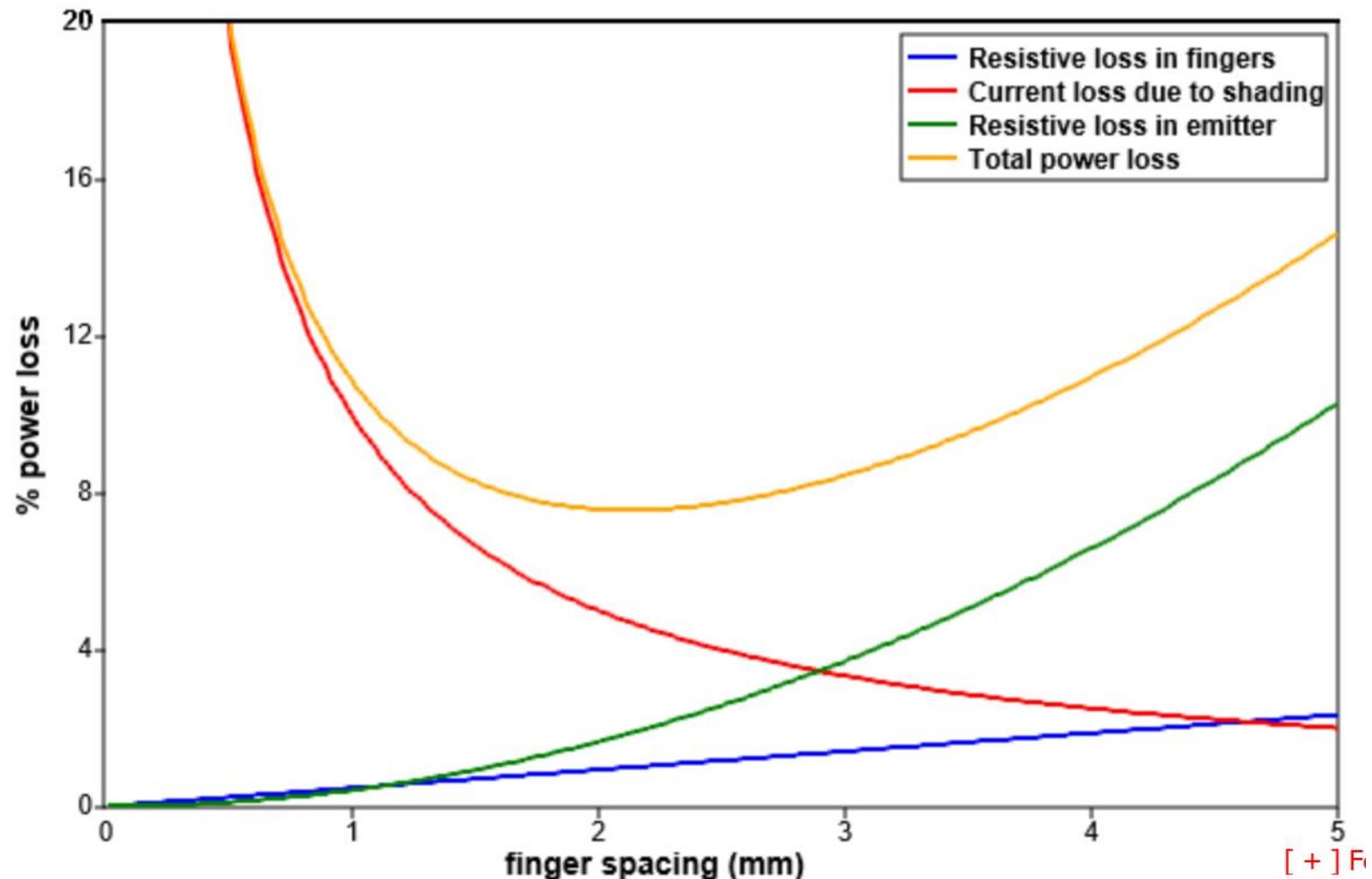
Rezistenta serie

- ▶ Minimizare R_s
 - bare colectoare
 - “degete”
- ▶ Comprimis
 - rezistenta
 - suprafata metalica reflectorizanta



Rezistenta serie

- ▶ Comprimis rezistenta/suprafata metalica



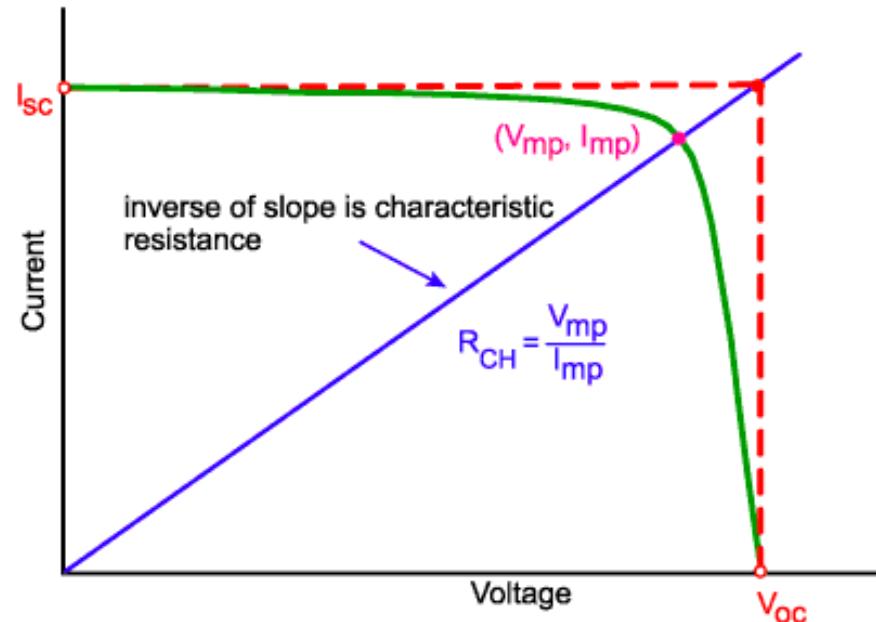
Rezistenta caracteristica

- ▶ Raportul intre V si I cand celula lucreaza la eficienta maxima

$$R_C = \frac{V_{pm}}{I_{pm}} \approx \frac{V_{OC}}{I_{SC}}$$

- ▶ Daca sarcina este egala cu R_C , celula lucreaza la eficienta maxima

- ▶ Tipic, celulele comerciale opereaza la tensiune mica si curent mare
 - ▶ conexiunile la celule trebuie sa aiba rezistente de ordinul $m\Omega$



$$R_C = \frac{0.6V}{9A} \approx 0.067\Omega$$

Eficienta celulei solare

- ▶ raportul dintre puterea electrica generata si puterea optica incidenta

$$\eta = \frac{P_m}{P_o} = \frac{V_{pm} \cdot I_{pm}}{P_o}$$

$$\eta = \frac{P_m}{P_o} = \frac{V_{oc} \cdot I_{sc} \cdot FF}{P_o}$$

- ▶ Puterea optica depinde de fluxul energetic al luminii incidente si suprafata celulei

$$P_o = S \cdot \int_0^{\infty} \Phi_e(\lambda) d\lambda$$

Eficiența celulei solare

- ▶ determină suprafața necesară pentru obținerea unei puteri dorite

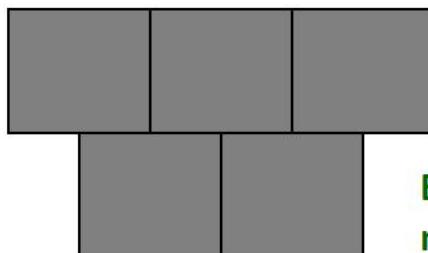
100% efficiency

(impossible to achieve)



20% efficiency

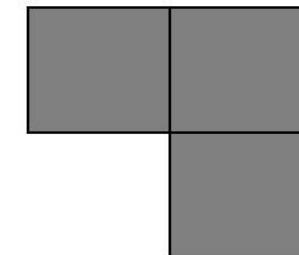
(monocrystalline
silicon solar cells)



Expensive
material

33% efficiency

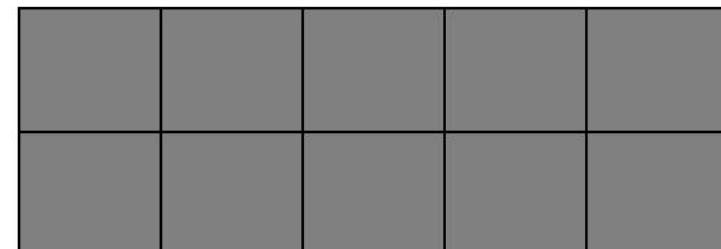
(space-grade solar cells)



Very
Expensive
material

10% efficiency

(thin film material)



Relatively Inexpensive material

Eficienta celulei solare

- ▶ Există o limită maximă teoretică pentru fiecare material semiconductor
 - fiecare material are o banda spectrală proprie, **mai mică** decât banda spectrală a soarelui
- ▶ valorile nu sunt foarte mari
 - din motive economice, recordurile nu sunt repetate în practică

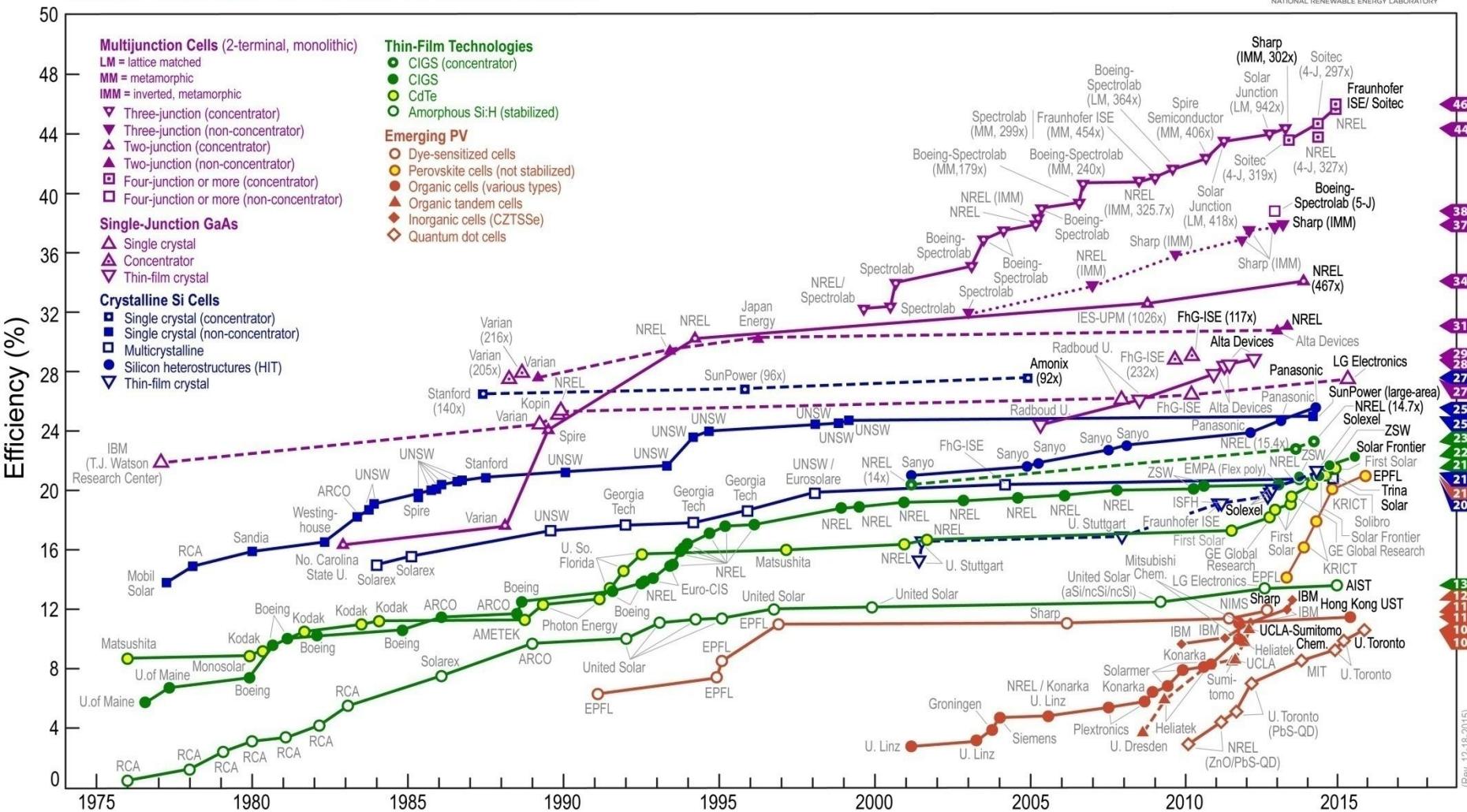
Table 1.1. Performance of some types of PV cell [Green *et al.*, 2001].

Cell Type	Area (cm ²)	V _{oc} (V)	J _{sc} (mA/cm ²)	FF	Efficiency (%)
crystalline Si	4.0	0.706	42.2	82.8	24.7
crystalline GaAs	3.9	1.022	28.2	87.1	25.1
poly-Si	1.1	0.654	38.1	79.5	19.8
a-Si	1.0	0.887	19.4	74.1	12.7
CuInGaSe ₂	1.0	0.669	35.7	77.0	18.4
CdTe	1.1	0.848	25.9	74.5	16.4

Eficienta maxima a celulei solare

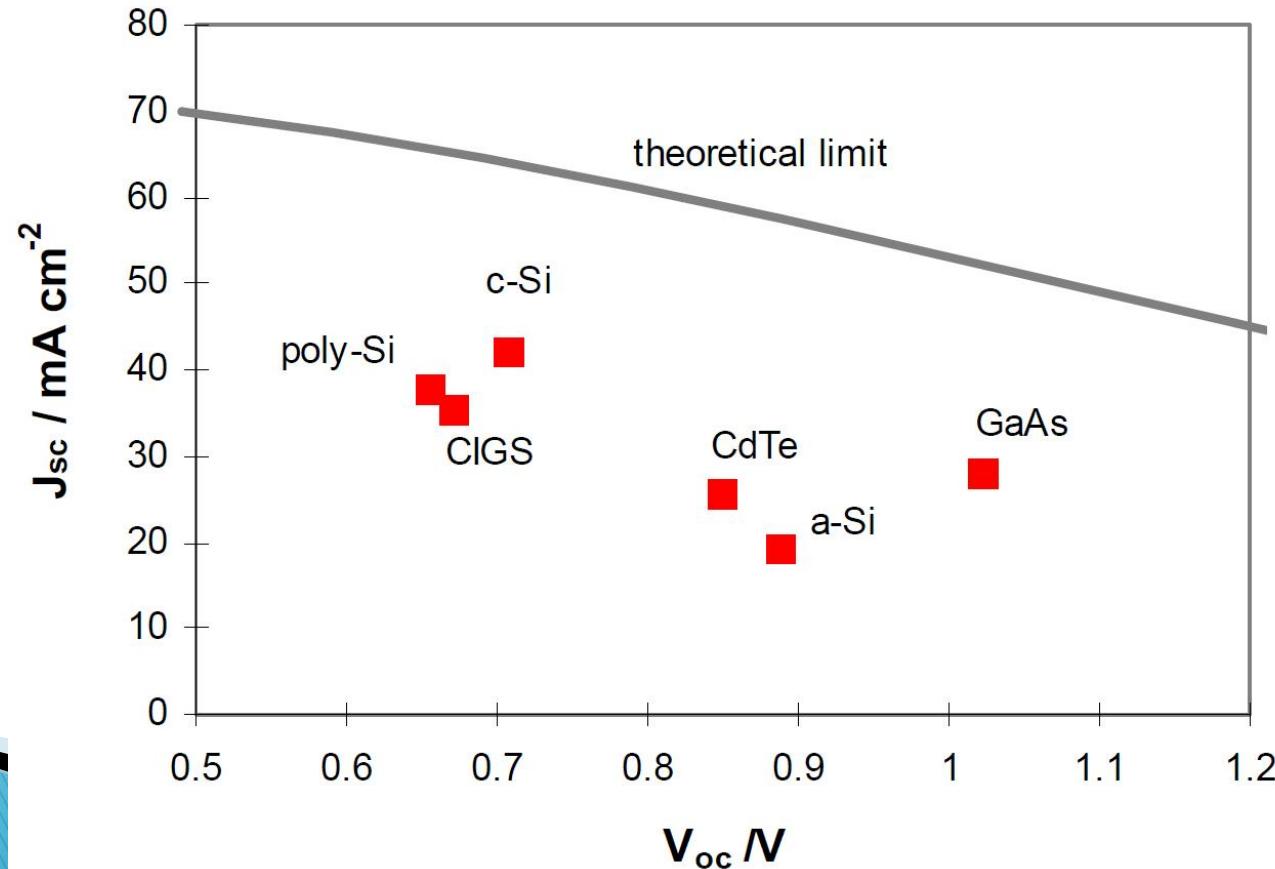
Best Research-Cell Efficiencies

NREL
NATIONAL RENEWABLE ENERGY LABORATORY



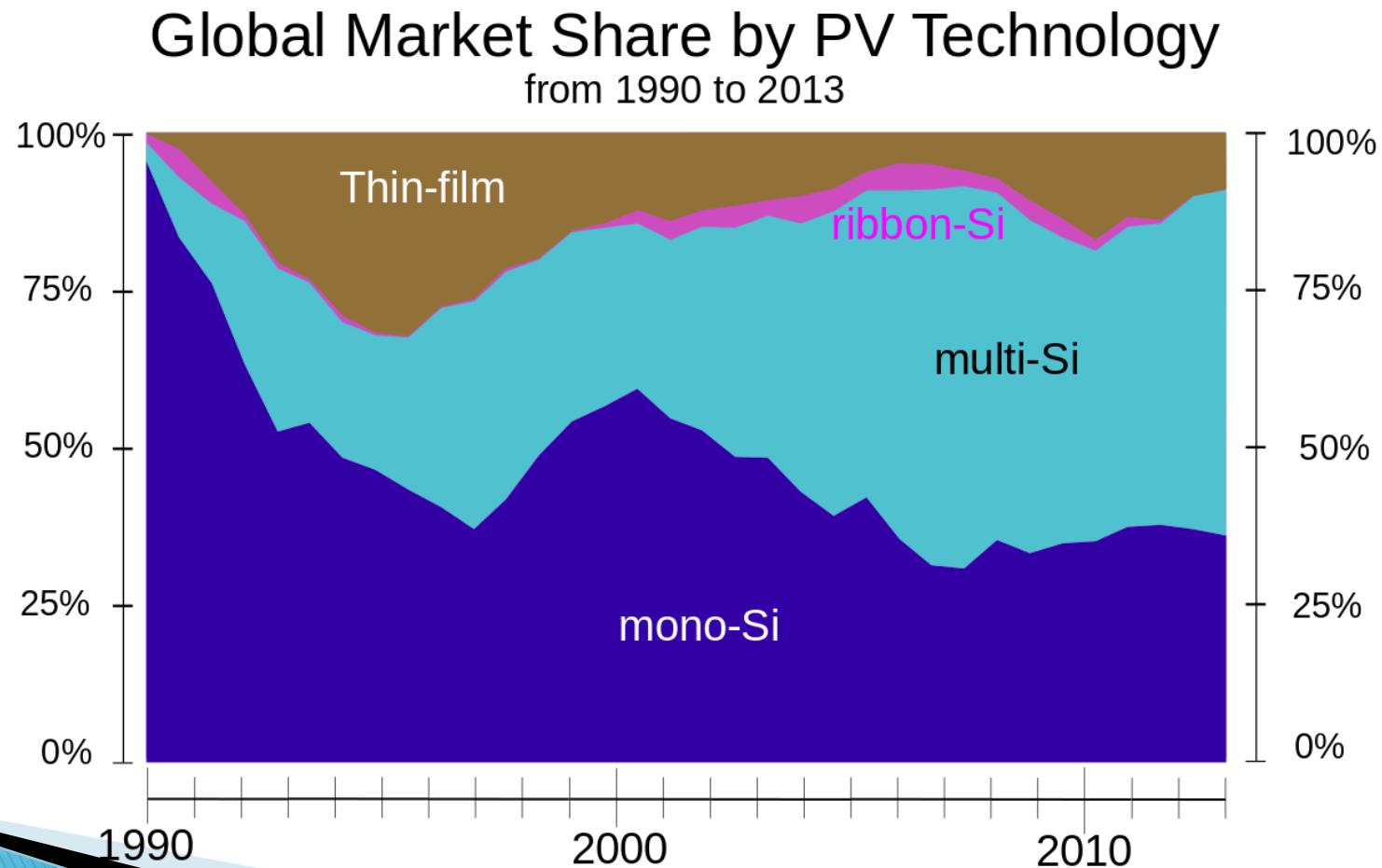
Dependenta de material

- ▶ materialele care ofera tensiuni mari au de obicei curenti mai mici
 - dependent de latimea benzii interzise



Realizari practice

- ▶ materialul preferat este Si



Tipic

80 WATT

POWERFUL PERFORMANCE. SHARP RELIABILITY.

POLY-CRYSTALLINE SILICON PHOTOVOLTAIC MODULE WITH 80W MAXIMUM POWER

Sharp's NE-80EJA photovoltaic modules offer industry-leading performance, durability, and reliability for a variety of electrical power requirements. Using breakthrough technology perfected by Sharp's 45 years of research and development, these modules incorporate an advanced surface texturing process to increase light absorption and improve efficiency. Common applications include cabins, solar power stations, pumps, beacons,



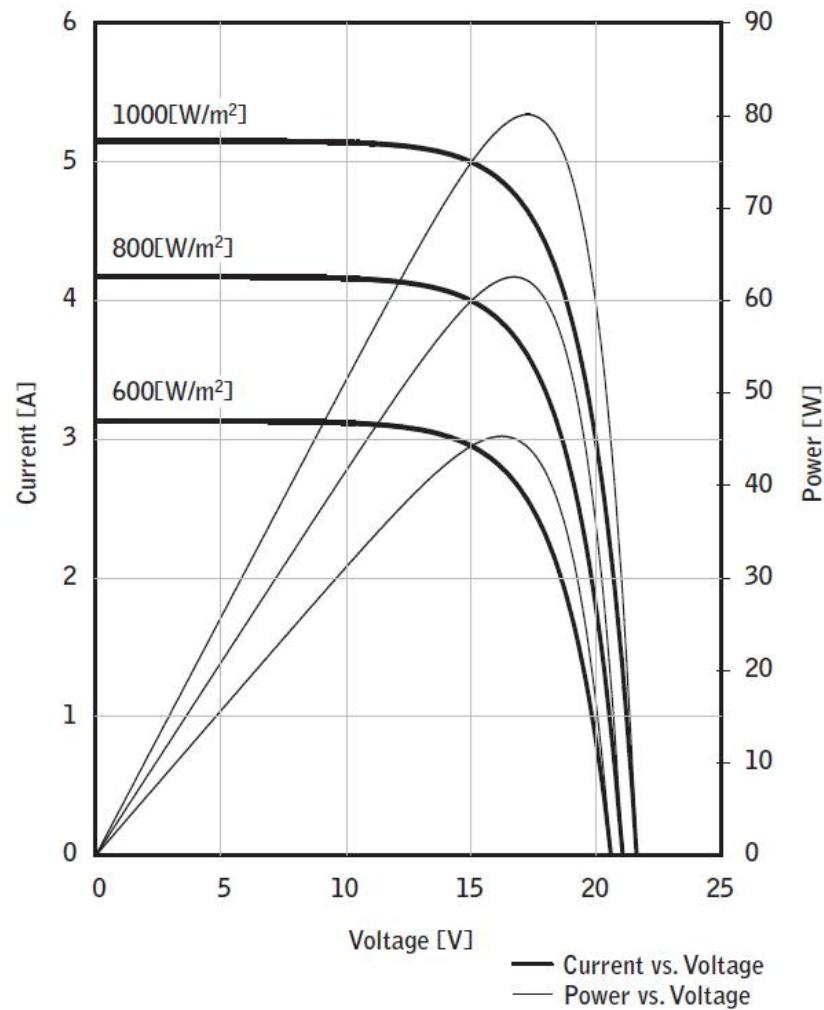
Tipic

ELECTRICAL CHARACTERISTICS

Cell	Poly-crystalline silicon
No. of Cells and Connections	36 in series
Open Circuit Voltage (Voc)	21.6V
Maximum Power Voltage (Vpm)	17.3V
Short Circuit Current (Isc)	5.16A
Maximum Power Current (Ipm)	4.63A
Maximum Power (Pmax)*	80W (+10% / -5%)
Module Efficiency (η_m)	12.40%
Maximum System Voltage	600VDC
Series Fuse Rating	10A
Type of Output Terminal	Junction Box

IV CURVES

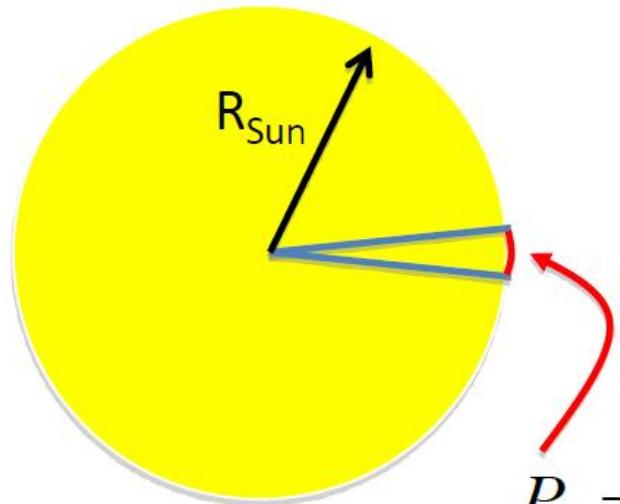
Cell Temperature: 25°C



Current, Power vs. Voltage Characteristics

Energia solară disponibilă

Sun



$$P_o = \sigma \cdot T^4$$

Total Radiative
Power of Sun (from
Stefan-Boltzmann
law, $T = 5762 \pm 50\text{K}$)

Power radiated
per unit area
 6.250×10^7
 W/m^2

Assumes Sun is a “black body.”

Energia solara disponibila

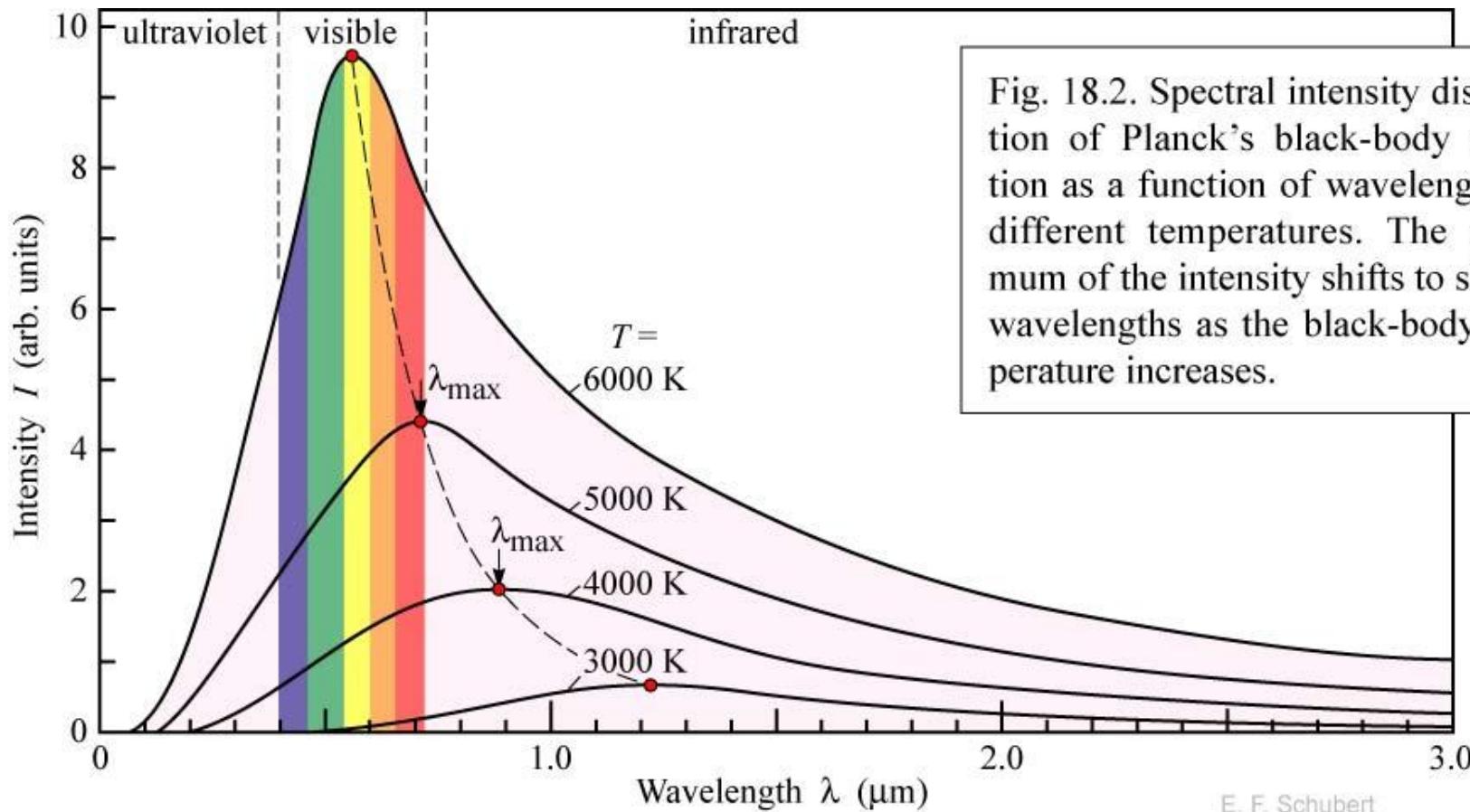
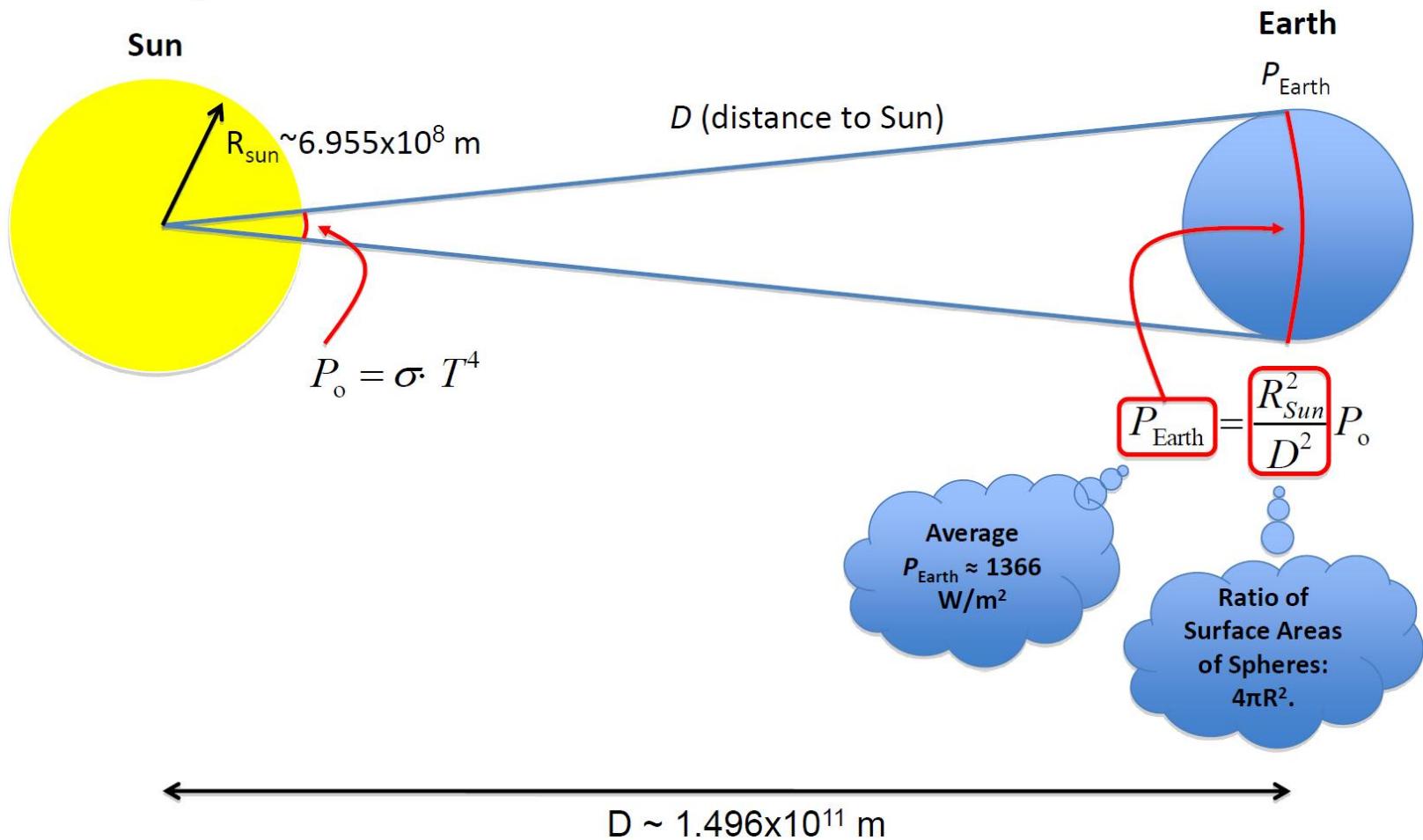


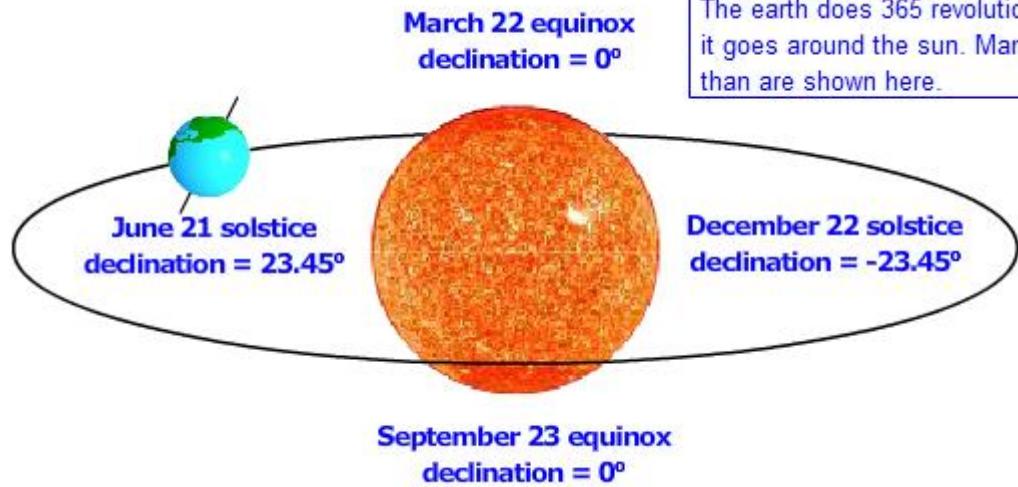
Fig. 18.2. Spectral intensity distribution of Planck's black-body radiation as a function of wavelength for different temperatures. The maximum of the intensity shifts to shorter wavelengths as the black-body temperature increases.

Energia solară disponibilă



Energia receptionată pe toata suprafața Pamantului
intr-o ora mai mare decat toata energia consumata
de intreaga populatie intr-un an

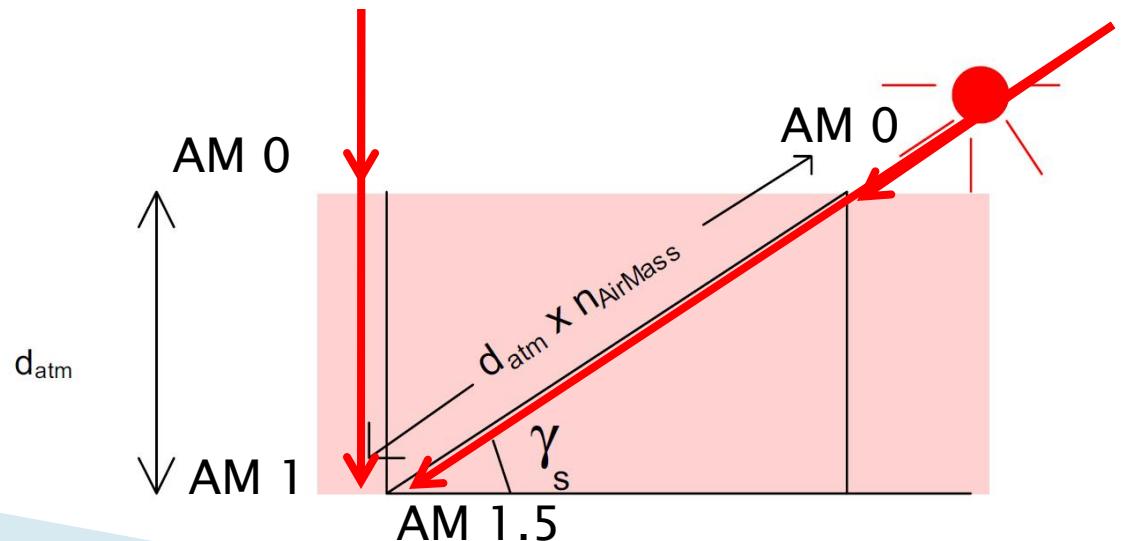
Energia solară disponibilă



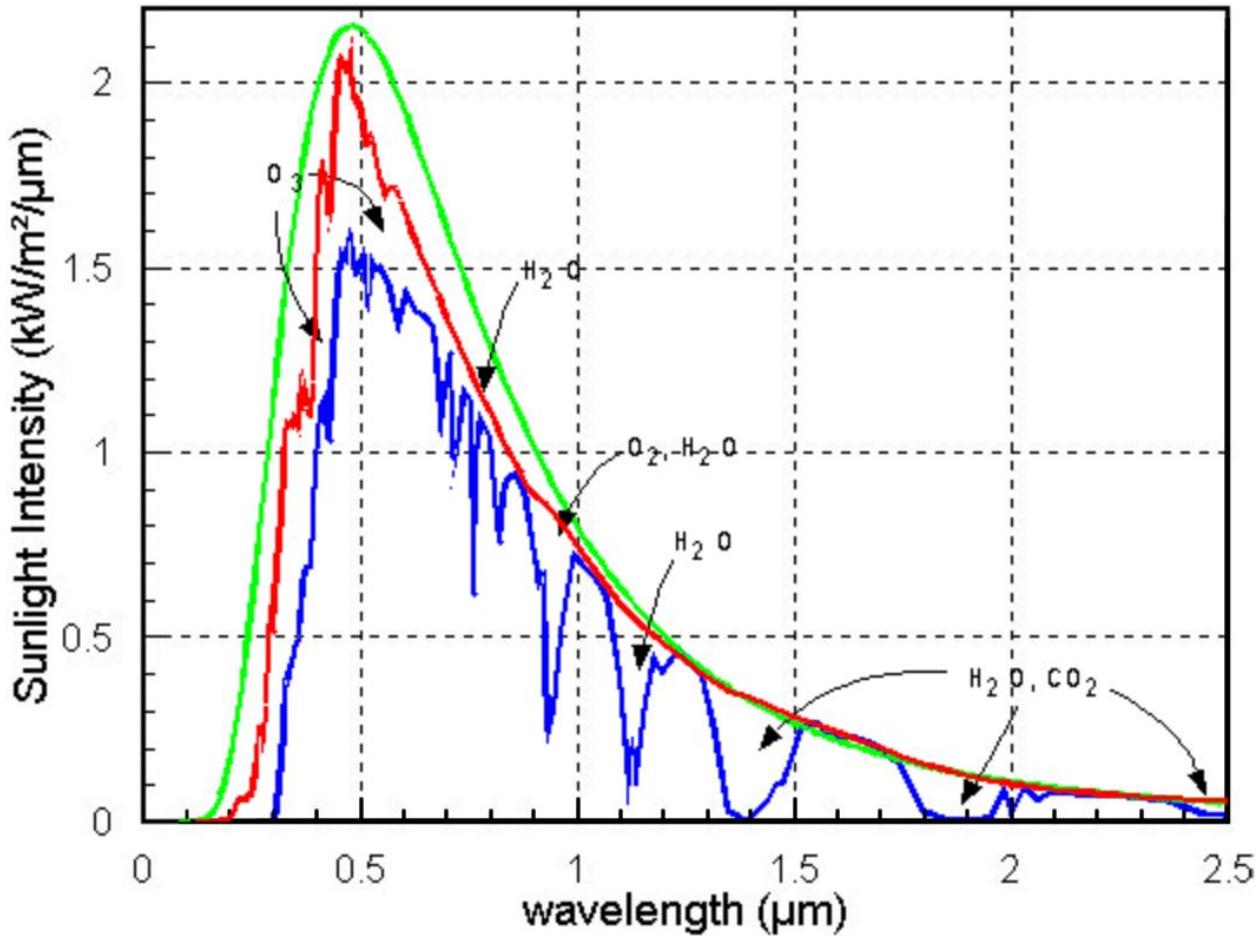
AM 0 = radiatia în afara atmosferei terestre

AM 1 = radiatia la suprafața terestră, incidentă normală

AM 1.5 = radiatia la suprafața terestră, incidentă corespunzătoare latitudinii de 48° (**standard**)

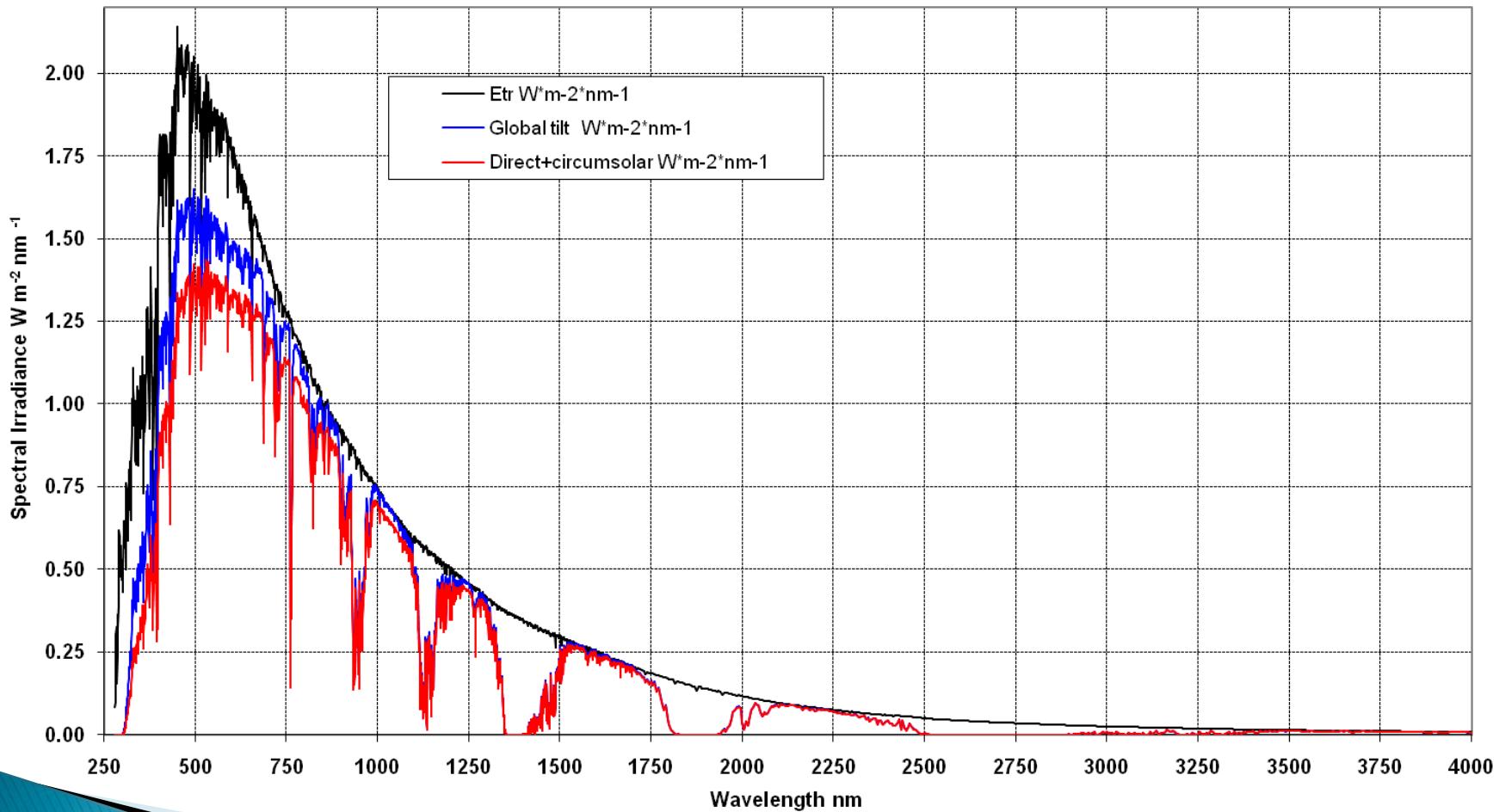


Energia solara disponibila

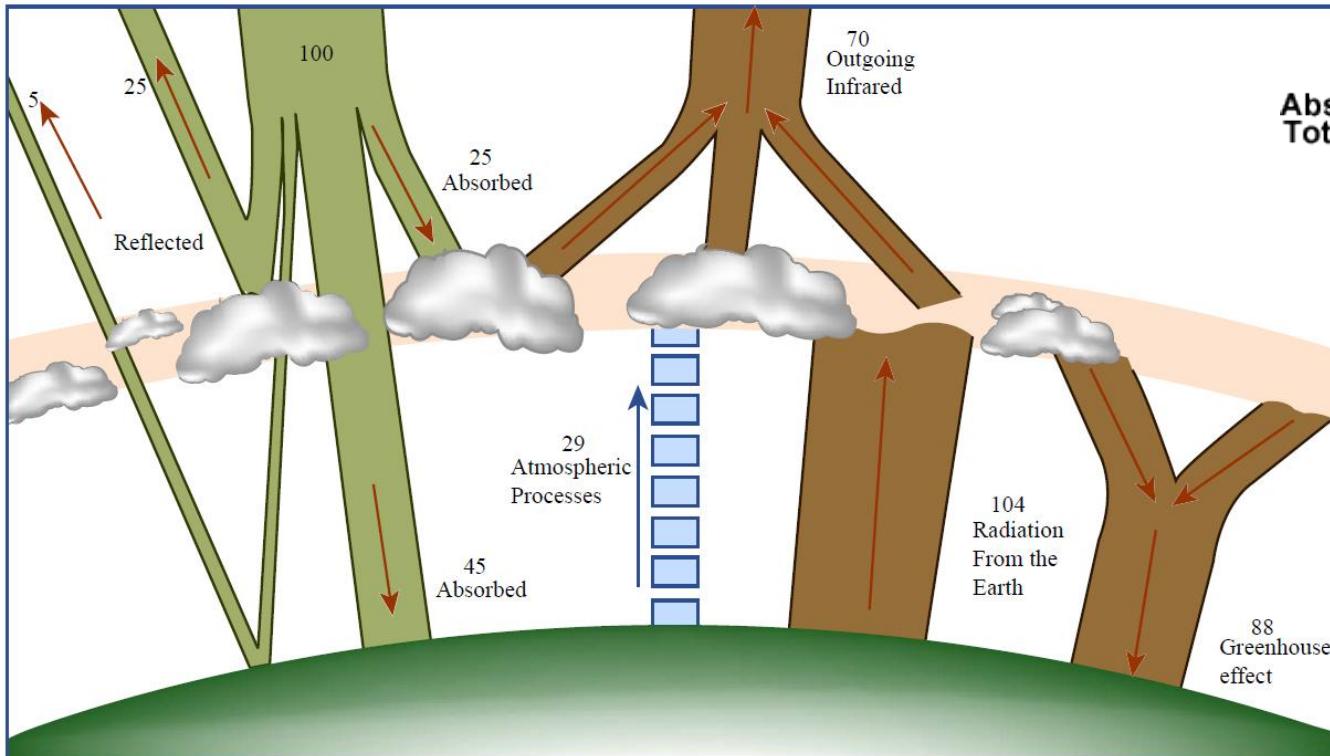


Energia solar disponibila

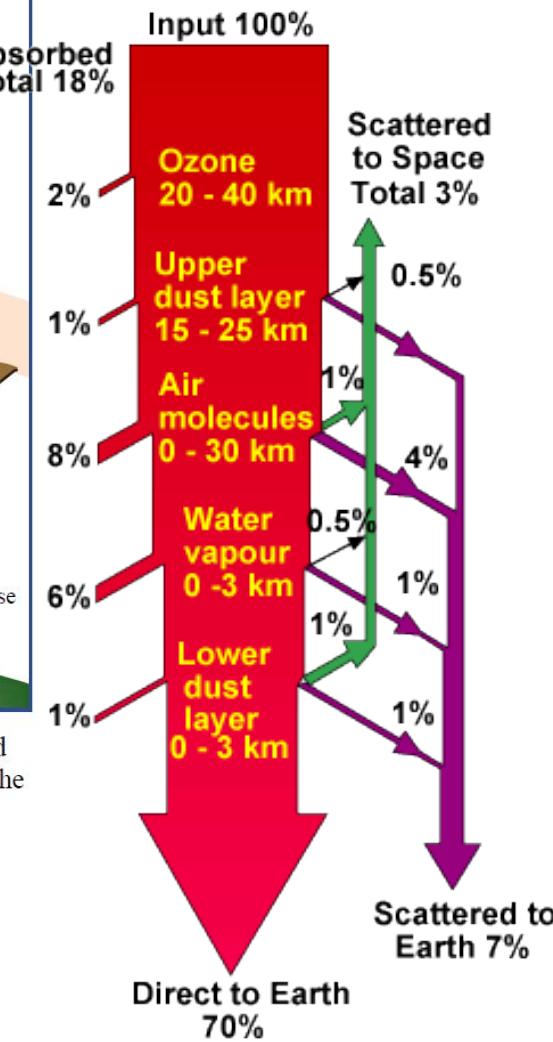
ASTM G173-03 Reference Spectra



Energia solara disponibila



Heat trapping in the atmosphere dominates the earth's energy balance. Some 30% of incoming solar energy is reflected (left), either from clouds and particles in the atmosphere or from the earth's surface; the remaining 70% is absorbed. The absorbed energy is reemitted at infrared wavelengths by the atmosphere (which is also heated by updrafts and cloud formation) and by the surface. Because most of the surface radiation is trapped by clouds and greenhouse gases and returned to the earth, the surface is currently about 33 degrees Celsius warmer than it would be without the trapping.



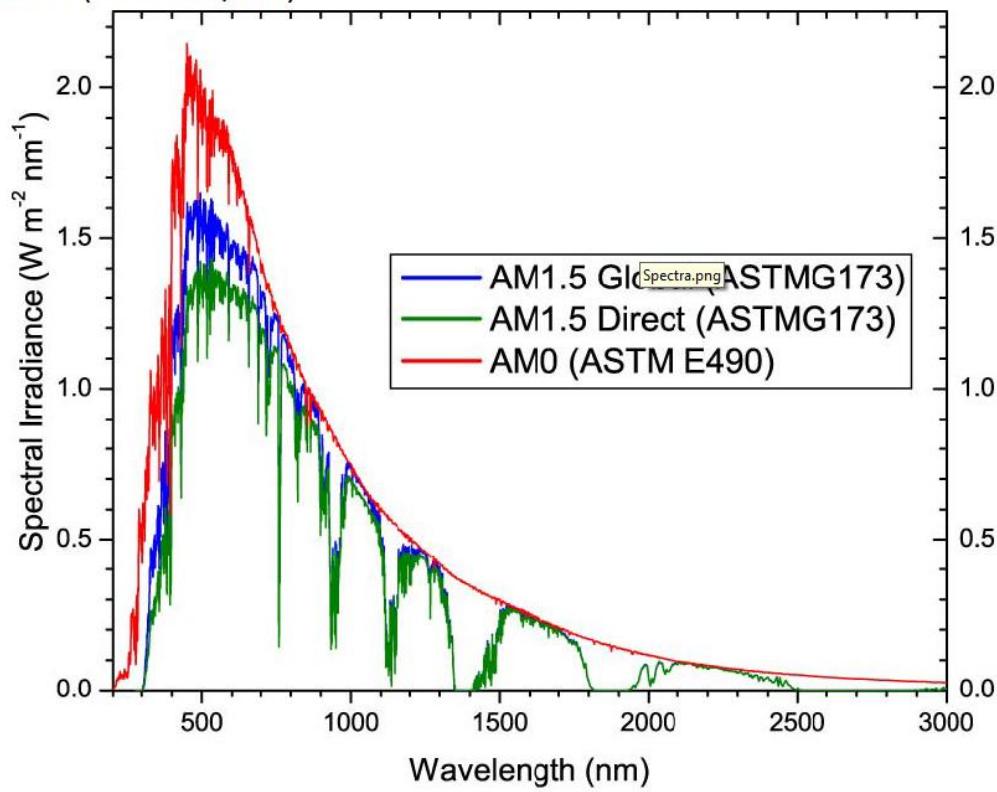
Energia solara disponibila

SOLAR SPECTRUM

AM1.5 Global: Used for testing of Flat Panels (Integrated power intensity: 1000 W/m²)

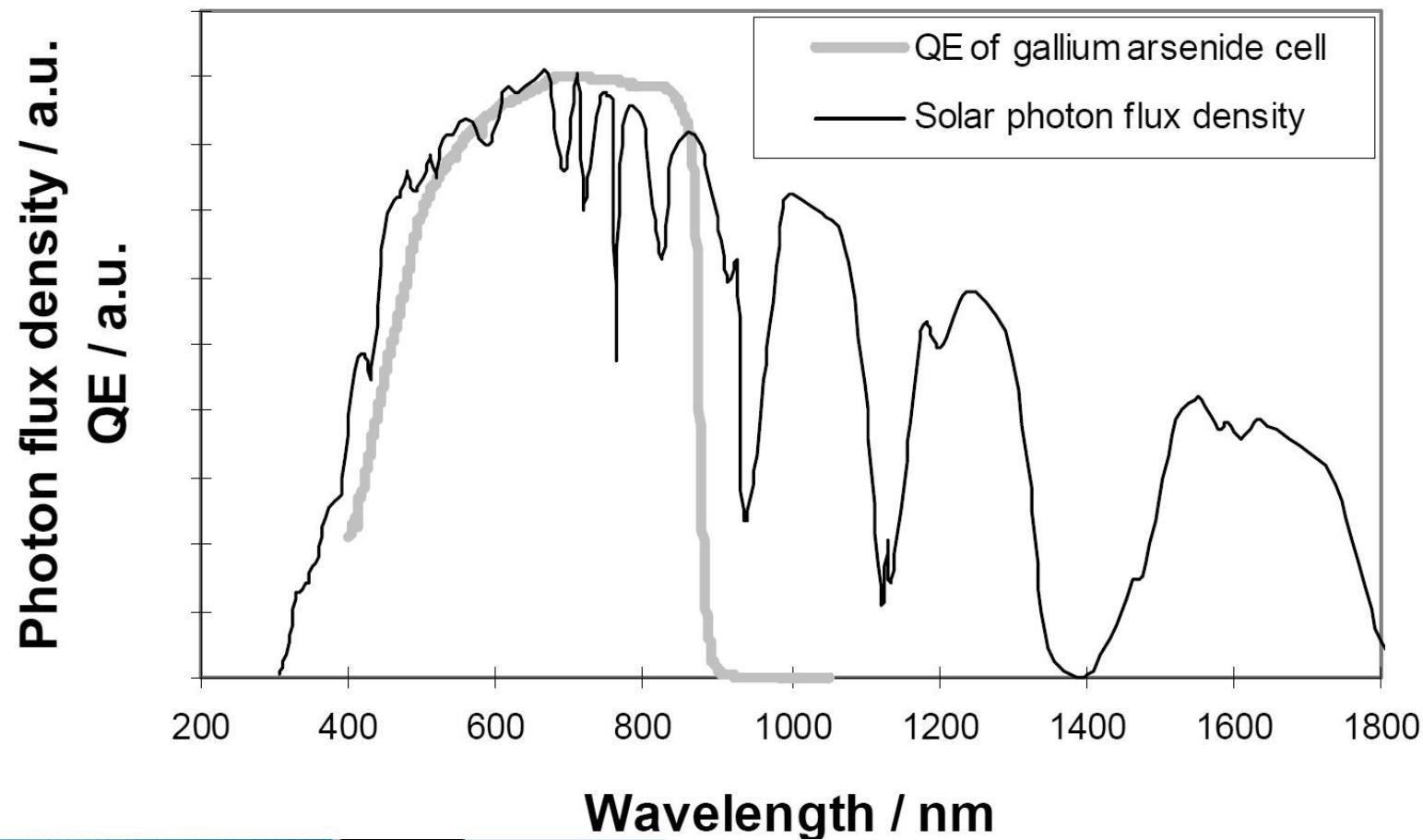
AM1.5 Direct: Used for testing of concentrators (900 W/m²)

AM0: Outer space (1366 W/m²)



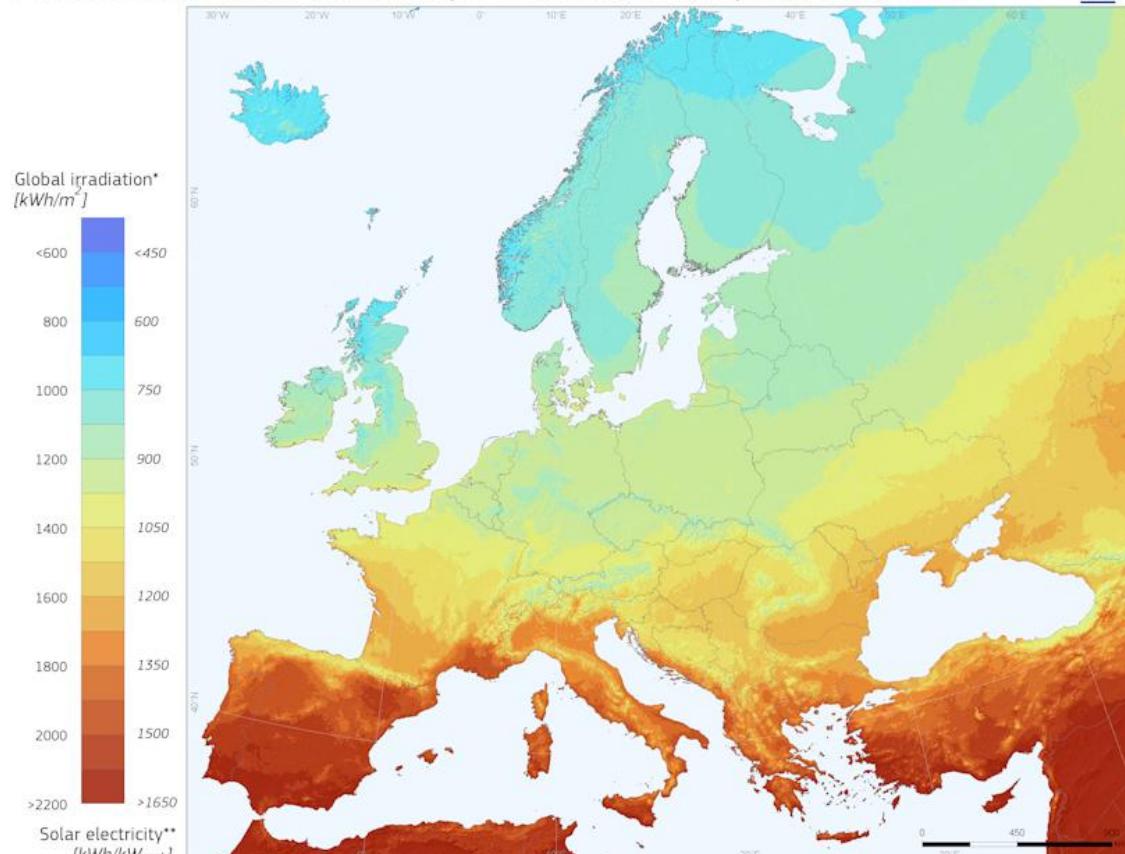
Motivatie eficienta limitata

- ▶ Toate materialele utilizeaza o banda care acopera **doar** partial spectrul solar (ex. GaAs)



Energia solara disponibila

Photovoltaic Solar Electricity Potential in European Countries



© European Union, 2012
PVGIS <http://re.jrc.ec.europa.eu/pvgis/>

Authors: Thomas Huld, Irene Pinedo-Pascua
EC - Joint Research Centre
In collaboration with: CM SAF, www.camsaf.eu

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<http://re.jrc.ec.europa.eu/pvgis/>

Energia solară disponibilă



Global irradiation and solar electricity potential

Optimally-inclined photovoltaic modules

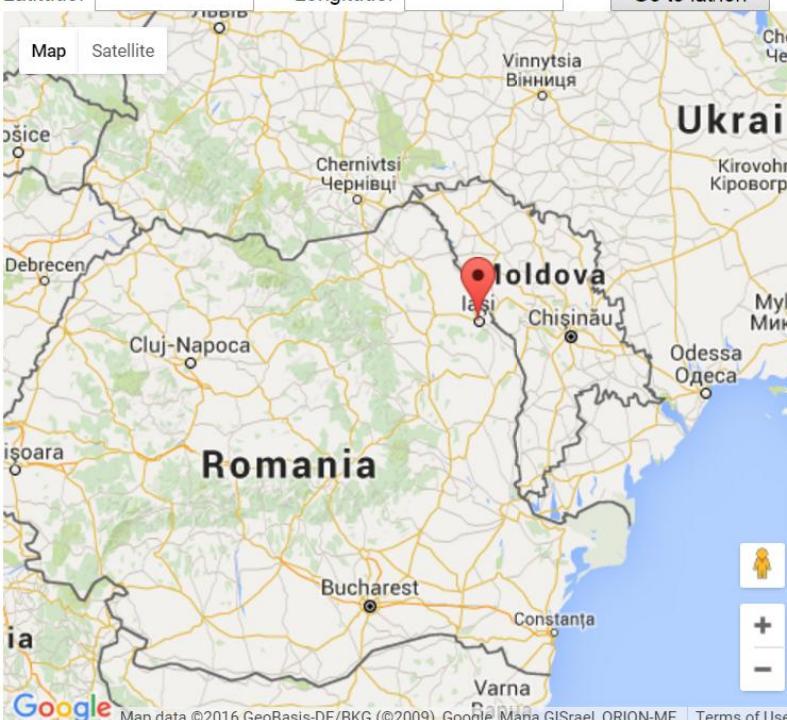
ROMANIA / ROMÂNIA



Energia solară disponibilă

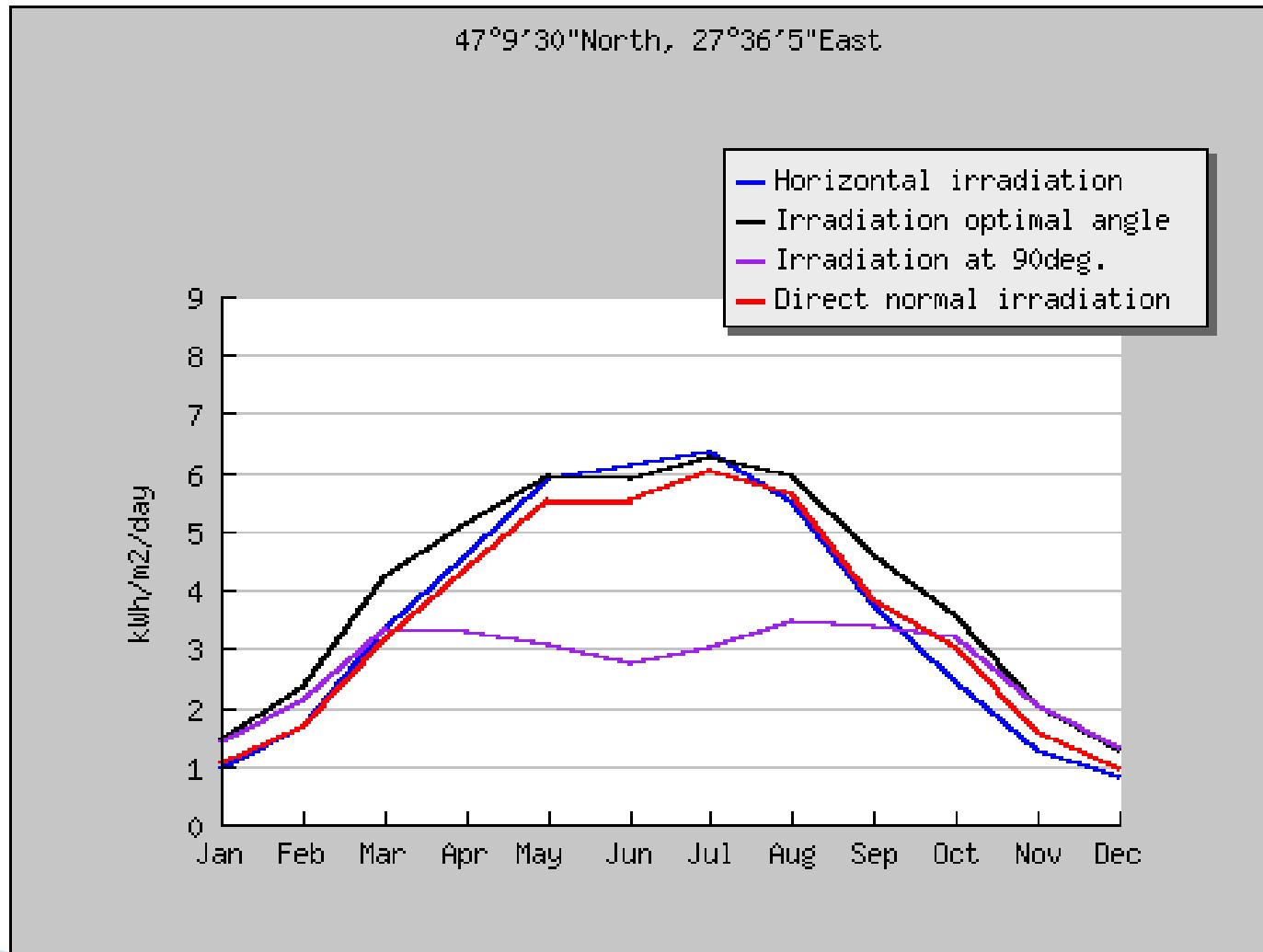
JRC
EUROPEAN COMMISSION
CM SAF
Photovoltaic Geographical Information System - Interactive Maps
EUROPA > EC > JRC > IE > RE > SOLAREC > PVGIS > Interactive maps > europe
Contact Important legal notice

cursor position:
46.725, 31.882
selected position:
47.158, 27.601

e.g., "Ispra, Italy" or "45.256N, 16.9589E"
lasi
Search
Latitude: Longitude: Go to lat/lon
Map Satellite

Horizontal irradiation
Irradiation at opt. angle
Direct normal irradiation
Irradiation at chosen angle: 90 deg.
Linke turbidity
Dif. / global radiation
Optimal inclination angle
Climate-SAF PVGIS
Average daytime temperature
Daily average of temperature
Number of heating degree days
Show graphs
Web page
Show horizon
Text file
PDF
Calculate [help]
[help]
Map data ©2016 GeoBasis-DE/BKG (©2009), Google, Mapa GISrael, ORION-ME | Terms of Use
Solar radiation Temperature Other maps

<http://re.jrc.ec.europa.eu/pvgis/>

Energia solara disponibila – Iasi



Unghi optim de inclinare

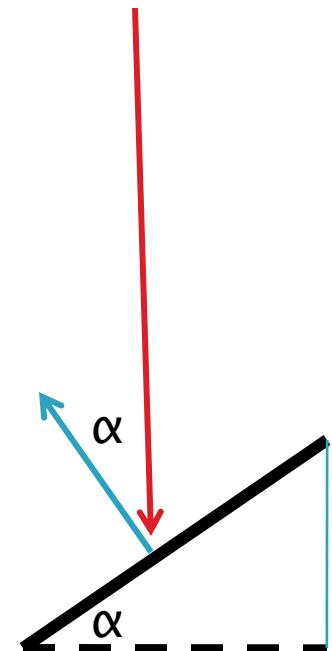
- ▶ Puterea optica depinde de fluxul energetic al luminii incidente si suprafata celulei
 - la **incidenta normală**
 - la **incidenta oarecare**

$$P_o = S \cdot \int_0^{\infty} \Phi_e(\lambda) d\lambda$$

◦ la **incidenta oarecare**

$$\Phi_e(\lambda) = \int_{\Sigma} \vec{S} \cdot \vec{n} dA = |S| \cdot A \cdot \cos \alpha$$

$$\vec{S} = \vec{E} \times \vec{H}$$



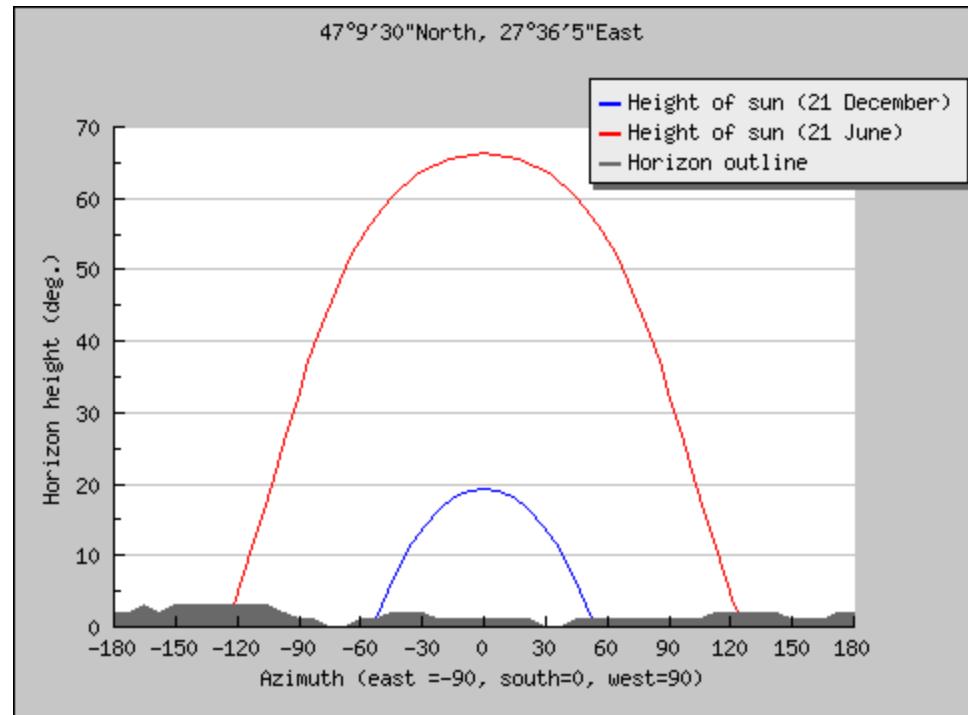
Unghi optim de inclinare

- ▶ Pozitia soarelui este diferita
 - in functie de ora
 - in functie de anotimp

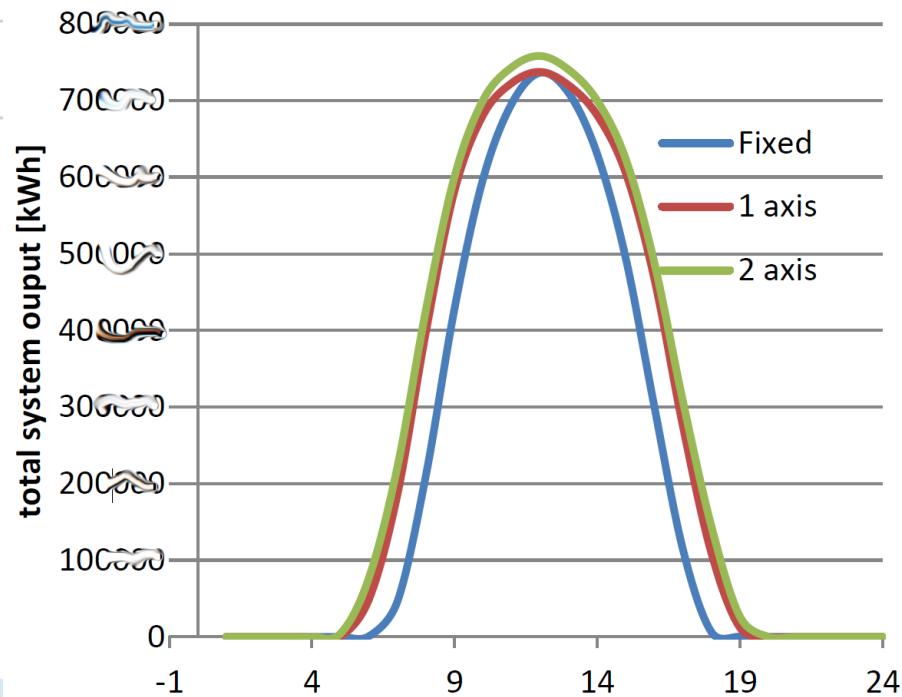
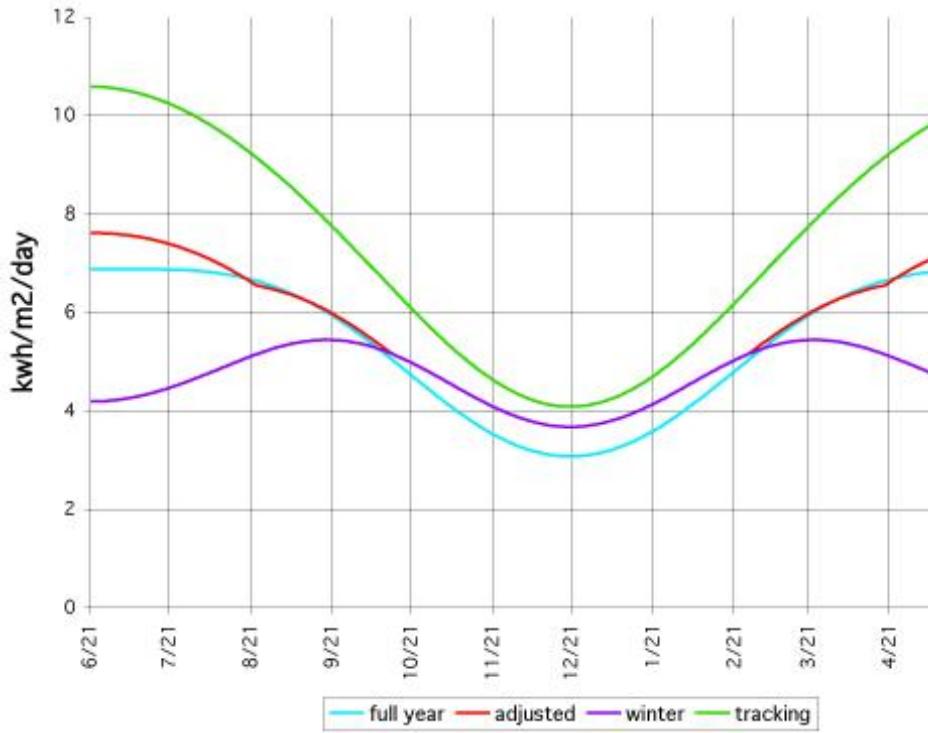


Sisteme de urmarire

- ▶ Sisteme motorizate de urmarire a soarelui
 - o axă
 - două axe
- ▶ Reglaj
 - fix (optim an)
 - două pozitii (anotimp)

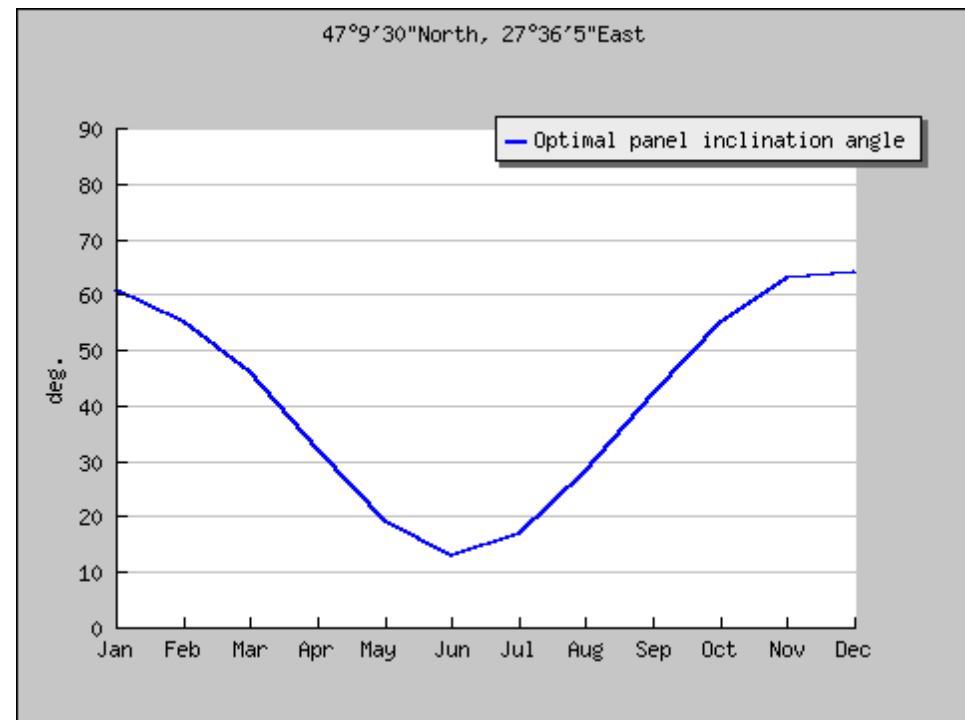


Sisteme de urmarire

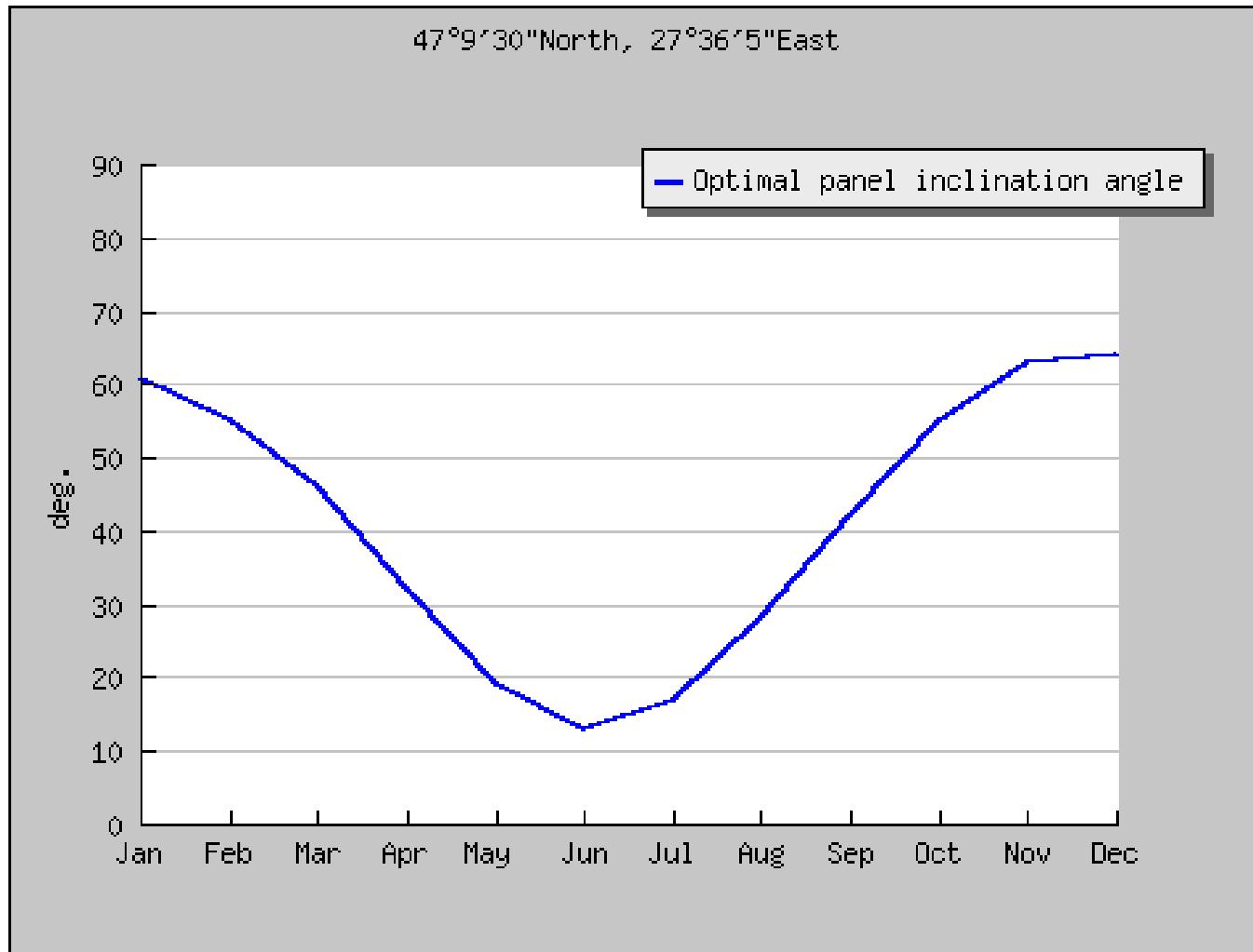


Unghi optim de inclinare

- ▶ Panourile se orienteaza spre sud (**geografic**)
- ▶ Inclinarea pe verticala se poate calcula din considerente
 - geometrice
 - astronomice

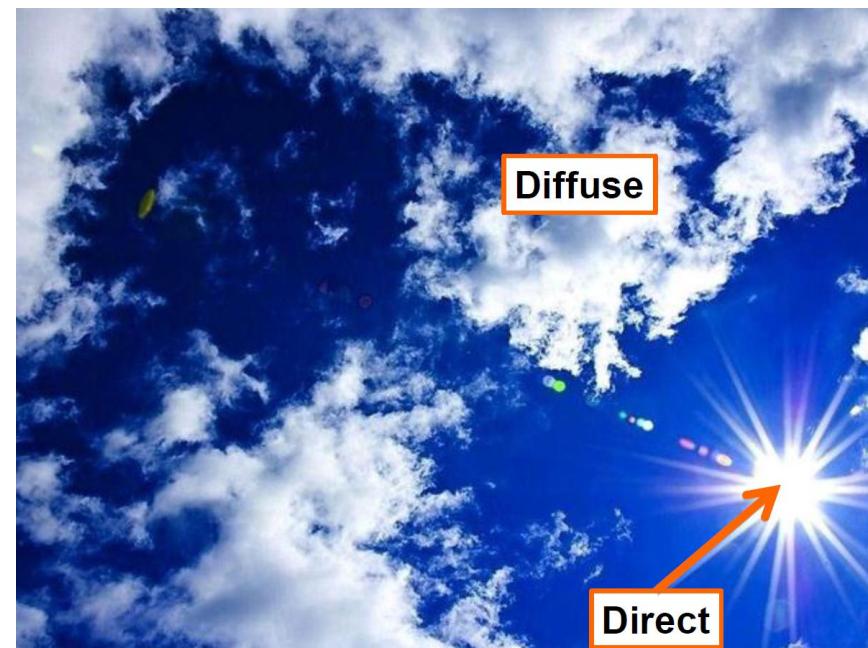
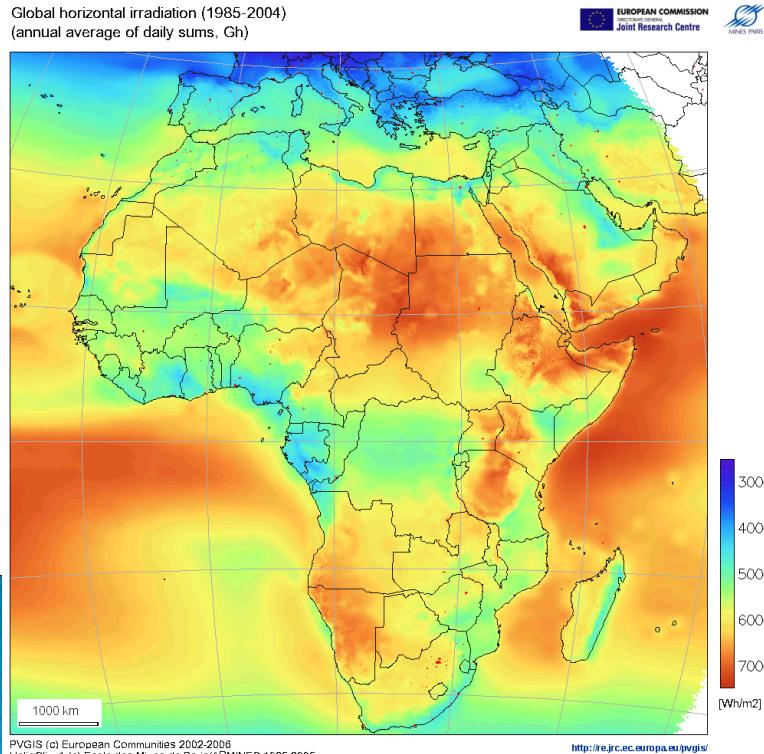


lasi

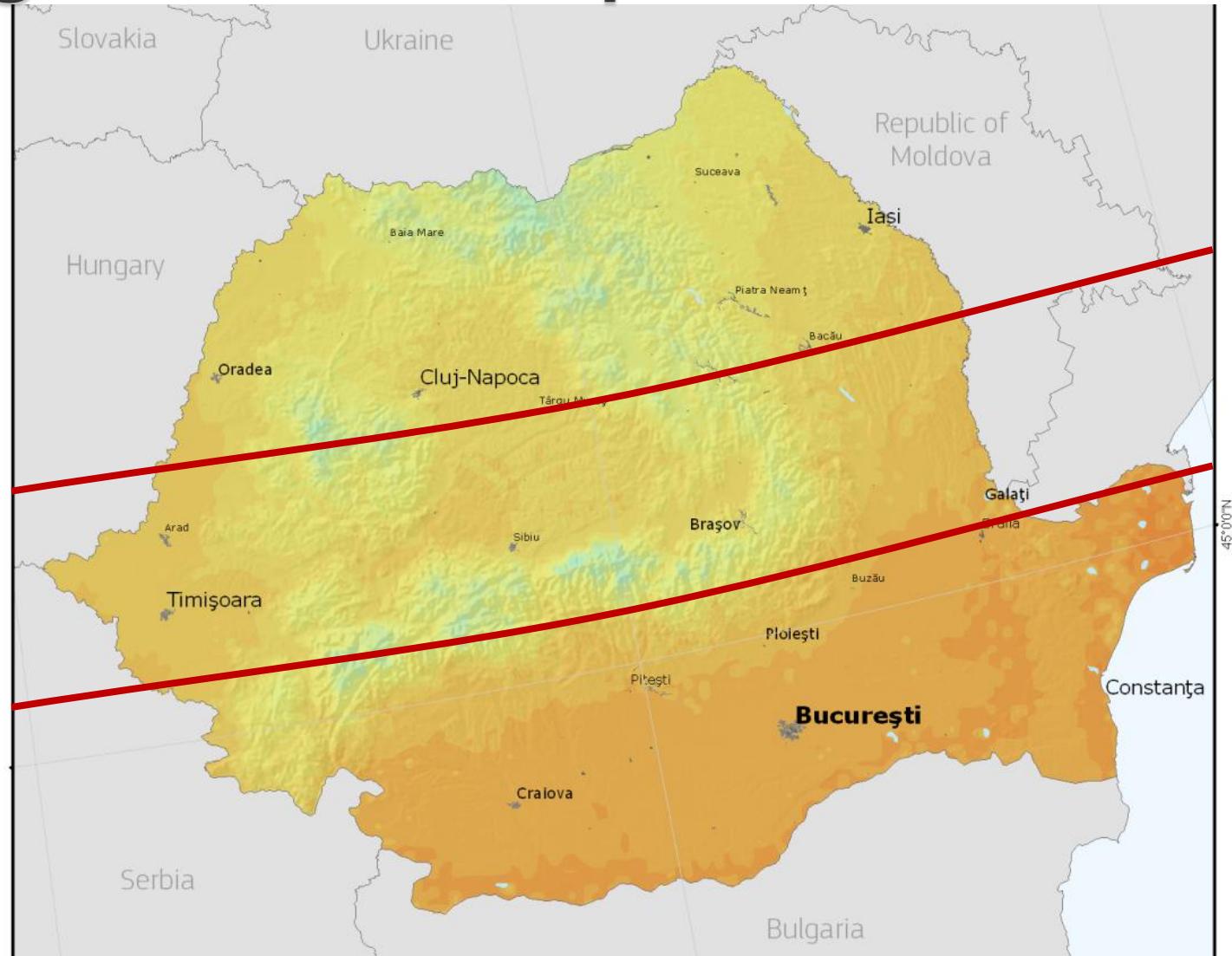


Tip de sistem de urmarire

- ▶ depinde de tipul de sistem solar
 - cu concentrare
 - fara concentrare
- ▶ depinde de conditii meteorologice



Energia solară disponibilă



lasí

Month	H _h	H _{opt}	H(90)	DNI	I _{opt}	T _{24h}
Jan	956	1440	1410	1020	61	-2.5
Feb	1680	2350	2130	1670	55	-1.4
Mar	3310	4210	3330	3150	46	4.0
Apr	4580	5150	3280	4380	32	10.6
May	5900	5960	3070	5530	19	16.7
Jun	6140	5900	2760	5530	13	20.0
Jul	6320	6240	3010	6010	17	22.3
Aug	5470	5960	3460	5630	28	21.4
Sep	3720	4600	3390	3820	42	16.1
Oct	2450	3570	3210	3000	55	10.2
Nov	1260	2000	2010	1600	63	5.5
Dec	802	1280	1310	959	64	-0.8
Year	3560	4070	2700	3540	35	10.2

Mont h	H_h	H_{opt}	$H(90)$	DNI	I_{opt}	T_{24h}
Jan	956	1440	1410	1020	61	-2.5
Feb	1680	2350	2130	1670	55	-1.4
Mar	3310	4210	3330	3150	46	4.0
Apr	4580	5150	3280	4380	32	10.6
May	5900	5960	3070	5530	19	16.7
Jun	6140	5900	2760	5530	13	20.0
Jul	6320	6240	3010	6010	17	22.3
Aug	5470	5960	3460	5630	28	21.4
Sep	3720	4600	3390	3820	42	16.1
Oct	2450	3570	3210	3000	55	10.2
Nov	1260	2000	2010	1600	63	5.5
Dec	802	1280	1310	959	64	-0.8
Year	3560	4070	2700	3540	35	10.2

H_h : Irradiation on horizontal plane (Wh/m²/day)

H_{opt} : Irradiation on optimally inclined plane (Wh/m²/day)

$H(90)$: Irradiation on plane at angle: 90deg. (Wh/m²/day)

DNI: Direct normal irradiation (Wh/m²/day)

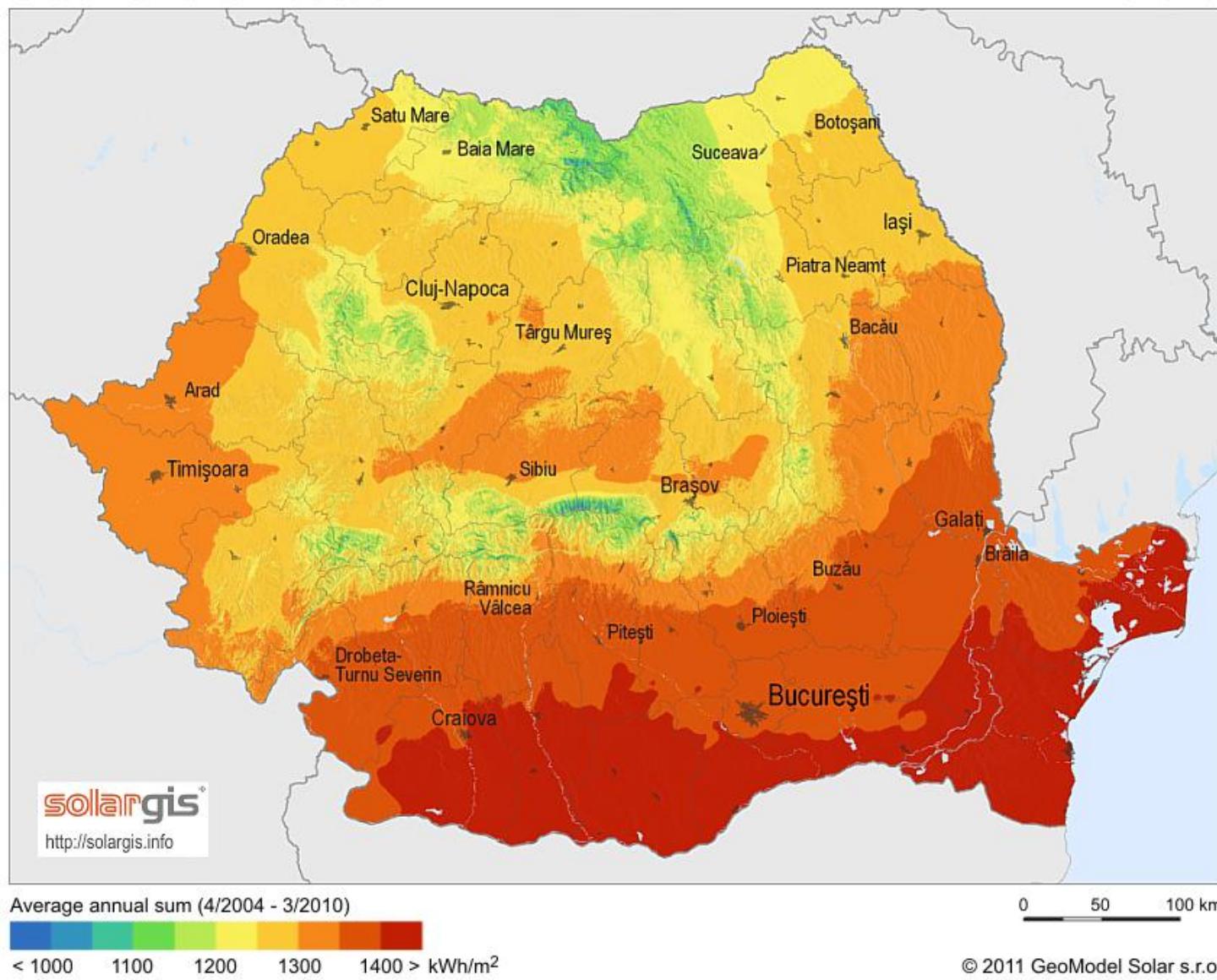
I_{opt} : Optimal inclination (deg.)

T_{24h} : 24 hour average of temperature (°C)

Romania

Global horizontal irradiation

Romania



Contact

- ▶ Laboratorul de microunde si optoelectronica
- ▶ <http://rf-opto.eti.tuiasi.ro>
- ▶ rdamian@etti.tuiasi.ro

- ▶ <http://ocw.mit.edu/>
- ▶ MIT Course Number 2.627
- ▶ Fundamentals of Photovoltaics

- ▶ <http://re.jrc.ec.europa.eu/pvgis/>
- ▶ <http://www.pveducation.org/>